

M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

SEMESTER – I

S. No.	Course	Course Name	Category	Hour	Hours per week		
	codes			L	T	P	
1.	21D57101	CMOS Analog IC Design	PC	3	0	0	3
2.	21D57102	CMOS Digital IC Design	PC	3	0	0	3
3.	21D57103a 21D57103b 21D57103c	Program Elective – I Microchip Fabrication Techniques Nanomaterials and Nanotechnology CAD for VLSI	PE	3	0	0	3
4.	21D57104a 21D57104b 21D57104c	Program Elective – II Device Modelling FPGA Architectures and Applications ASIC Design	PE	3	0	0	3
5.	21D57105	CMOS Analog IC Design Lab	PC	0	0	4	2
6.	21D57106	CMOS Digital IC Design Lab	PC	0	0	4	2
7.	21DRM101	Research Methodology and IPR	MC	2	0	0	2
8.	21DAC101a 21DAC101b 21DAC101c	Audit Course – I English for Research paper writing Disaster Management Sanskrit for Technical Knowledge	AC	2	0	0	0
	•	Total	•			•	18



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

SEMESTER – II

S.No.	Course	Course Name	Category	Hou	rs per	week	Credit
	codes			L	T	P	S
1.	21D57201	CMOS Mixed Signal IC Design	PC	3	0	0	3
2.	21D57202	Physical Design Automation	PC	3	0	0	3
3.	21D57203a 21D57203b 21D57203c	Program Elective – III SoC Testing and Verification Semiconductor Memory Design and Testing MEMS System Design	PE	3	0	0	3
4.	21D57204a 21D57204b 21D57204c	Program Elective – IV Low Power VLSI Design IoT and its Applications VLSI Signal Processing	PE	3	0	0	3
5.	21D57205	CMOS Mixed Signal IC Design Lab	PC	0	0	4	2
6.	21D57206	Physical Design Automation Lab	PC	0	0	4	2
7.	21D57207	Technical seminar	PR	0	0	4	2
8.	21DAC201a 21DAC201b 21DAC201c	Audit Course – II Pedagogy Studies Stress Management for Yoga Personality Development through Life Enlightenment Skills	AC	2	0	0	0
		Total					18



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

SEMSTER - III

S.No.	Course	Course Name	Categor	Hou	Hours per		
	codes		\mathbf{y}	L	T	P	ts
1.	21D57301a 21D57301b 21D06203a	Program Elective – V Bi-CMOS Technology and Applications Optimization Techniques and Applications in VLSI Design SoC Architecture	PE	3	0	0	3
2.	21DOE301b 21DOE301c 21DOE301e	Open Elective Industrial Safety Business Analytics Waste to Energy	OE	3	0	0	3
3.	21D57302	Dissertation Phase – I	PR	0	0	20	10
4.	21D57303	Co-curricular Activities					2
		Total					18

SEMESTER - IV

S.No.	Course	Course Name	Category	Hou	ırs p	er	Credits
	codes			L	T	P	
1.	21D57401	Dissertation Phase – II	PR	0	0	32	16
Total							16



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

	COMMON COURSE STRUCTURE & SYLLABI				
Course Code	CMOS ANALOG IC DESIGN	L	Т	P	C
21D57101	0.1.200 1.11.1.220 0 20 2.2011	3	0	0	3
	Semester			I	1
Course Objectiv	res:				
• This cou	rse focuses on theory, analysis and design of analog integrated	circ	cuits	in t	oth
Bipolar a	and Metal-Oxide-Silicon (MOS) technologies.				
Basic des	sign concepts, issues and tradeoffs involved in analog IC design are	exp	lored	i.	
 Intuitive 	understanding and real-life applications are emphasized throughout	the	cour	se.	
 To learn 	about Design of CMOS Op Amps, Compensation of Op Amps,	Des	sign	of T	wo-
Stage Op	Amps, Power Supply Rejection Ratio of Two-Stage Op Amps, Ca	sca	de O	p An	nps,
Measure	ment Techniques of OP Amp.				
 To know 	v about Characterization of Comparator, Two-Stage, Open-Loc	p (Com	parat	ors,
Improvir	g the Performance of Open-Loop Comparators, Discrete-Time Com	ıpar	ators	etc.	
	es (CO): Student will be able to				
 Design M 	OSFET based analog integrated circuits.				
 Analyze a 	nalog circuits at least to the first order.				
 Appreciat 	e the trade-offs involved in analog integrated circuit design.				
 Understar 	nd and appreciate the importance of noise and distortion in analog ci	rcui	ts.		
 Analyze 	complex engineering problems critically in the domain of analo	g I	ℂ de	sign	for
conductin	g research.				
 Solve eng 	ineering problems for feasible and optimal solutions in the core area	ì			
UNIT - I		Le	cture	Hrs	
	wice Physics: General Considerations, MOS I/V Characteristics				
	vice models and MOS Capacitor. Short Channel Effects and Device				
	- Basic Concepts, Common Source Stage, Source Follower, Com	mor	ı Ga	te St	age,
Cascode Stage.					
UNIT - II				Hrs	
	plifiers: Single Ended and Differential Operation, Basic Differentia				
	, Differential Pair with MOS loads, Gilbert Cell. Passive and				
	Current Mirrors, Cascode Current Mirrors, Active Current Mirrors.	Cur	rent	Stee	rıng
Circuit		T .	- 1	TT	_
UNIT - III	roma of Ammilificans/Consul Considerations Common Source			Hrs	
	ponse of Amplifiers: General Considerations, Common Source mon Gate Stage, Cascode Stage, Differential Pair. Noise – 7		-		
		• •			nse,
UNIT - IV	f Noise in circuits, Noise in single stage amplifiers, Noise in Differe			Hrs:	
	ifiers:General Considerations, Feedback Topologies, Effect of Load				
_	eneral Considerations, One Stage Op Amps, Two Stage Op Amps,	_	_		
_	ode Feedback, Input Range limitations, Slew Rate, Power S				_
	os, Stability and Frequency Compensation.	⊶PP	., 10	2,000	.011,
UNIT - V	z, z.m. no requency compensation	Le	cture	Hrs	
	haracterization of comparator, Two-Stage, Open-Loop comparato				
_	ors, Improving the Performance of Open-Loop Comparators			_	
Compara	The second secon	, –			

Comparators. **Textbooks:**

- 1. B.Razavi, "Design of Analog CMOS Integrated Circuits", 2ndEdition, McGraw Hill Edition2016.
- 2. Paul.R.Gray& Robert G. Meyer, "Analysis and Design of Analog Integrated Circuits", Wiley,



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

5thEdition, 2009.

- 1.T.C.Carusone, D.A.Johns&K.Martin, "Analog Integrated Circuit Design", 2ndEdition, Wiley, 2012.
- 2. P.E.Allen&D.R.Holberg, "CMOS Analog Circuit Design", 3rd Edition, Oxford University Press, 2011
- 3. R.Jacob Baker, "CMOS Circuit Design, Layout, and Simulation", 3rd Edition, Wiley, 2010.
- 4. Adel S. Sedra, Kenneth C. Smith, Arun, "Microelectronic Circuits", 6th Edition, Oxford University Press



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

	COMMON COURSE STRUCTURE & STLLABI				
Course Code	CMOS DIGITAL IC DESIGN	L	T	P	C
21D57102		3	0	0	3
	Semester			[
	•				
Course Object		. 1		OCT	TT
	erstand the fundamental properties of digital Integrated circuits using				
_	ns and to develop skills for various logic circuits using CMOS related	ı aes	ign s	tyres	•
	arse also involves analysis of performance metrics.				c
	th fundamentals of CMOS Digital integrated circuit design such a			ance	to
	logic, Combinational MOS logic circuits and Sequential MOS logic				
	th the fundamentals of Dynamic logic circuits and basic semicone			emo	ries
	re the basics for the design of high performance digital integrated cir	cuits	· .		
	nes (CO): Student will be able to				
	trate advanced knowledge in Static and dynamic characteristics of Cl	MOS	δ,		
	Delay and Power of Adders circuits.				
•	different semiconductor memories.				
	, design and implement combinational and sequential MOS logic circ				
 Analyze 	complex engineering problems critically in the domain of digital	al IC	des	sign	for
conducti	ng research.				
	gineering problems for feasible and optimal solutions in the core area	a of	digita	al IC	S
UNIT - I				Hrs:	
MOS Design P	seudo NMOS Logic:Inverter, Inverter threshold voltage, Output high	h vo	ltage	,	
Output Low vol	tage, Gain at gate threshold voltage, Transient response, Rise time, F	all ti	me,	Pseu	do
	tes, Transistor equivalency, CMOS Inverter logic.				
UNIT - II				Hrs:	
	MOS Logic Circuits: MOS logic circuits with NMOS loads, Primi				
	NAND gate, Complex Logic circuits design-Realizing Boolean e				
	nd CMOS gates, AOI and OIA gates, CMOS full adder, CMOS tra	ansm	issio	n ga	tes,
	Transmission gates.				
UNIT - III				Hrs:	
_	OS Logic Circuits: Behavior of bistable elements, SR Latch, Clock	ed la	atch	and	flip
flop circuits, Cl	MOS D latch and edge triggered flip-flop				
UNIT - IV		Lec	cture	Hrs:	
•	ic Circuits: Basic principle, Voltage Bootstrapping, Synchronou	•		•	
	its, Dynamic CMOS transmission gate logic, High performance l	Dyna	amic	CM	OS
circuits.					
UNIT - V				Hrs:	
	• Memories: Types, RAM array organization, DRAM – Types, Op				
currents in DR.	AM cell and refresh operation, SRAM operation Leakage currents	in S	SRA	M ce	lls,

Textbooks:

Flash Memory-NOR flash and NAND flash.

- 1. Neil Weste, David Harris, "CMOS VLSI Design: A Circuits and Systems Perspective", 4th Edition, Pearson, 2010
- 2. Digital Integrated Circuit Design Ken Martin, Oxford University Press, 2011.
- 3. CMOS Digital Integrated Circuits Analysis and Design Sung-Mo Kang, Yusuf Leblebici, TMH, 3rd Edition, 2011.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

- Introduction to VLSI Systems: A Logic, Circuit and System Perspective Ming-BO Lin, CRC Press, 2011
- 2. Digital Integrated Circuits A Design Perspective, Jan M.Rabaey, AnanthaChandrakasan, Borivoje Nikolic, 2ndEdition, PHI.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	MICROCHIP FABRICATION TECHNIQUES	L T P C
21D57103a	Program Elective – I	3 0 0 3
	Semester	I
Course Objectiv	ves:	
 Compreh 	nend impact of semiconductor industry on the design of developm	ent of integrated
circuits.		
 Acquaint 	with clean room technology	
 Understa 	nd oxidation methods, aspects of photolithography, diffusion,	ion implantation
technique	es.	
 Specify 	NMOS and CMOS design rules corresponding to 180r	nm, 90nm and
45nm tec	hnologies	
 Understa 	nd packaging principles	
	es (CO): Student will be able to	
Understar	nd various stages of fabrication	
	nd Various packaging techniques and Design rules.	
	various thin films and its characteristics.	
UNIT - I		Lecture Hrs:
Introduction to	Processing: Overview of semiconductor industry, Stages of Manuf	acturing. Process
	ends, Crystal growth, Basic wafer fabrication operations,	
	material preparation, Yield measurement, Contamination source	
construction.		•
UNIT - II		Lecture Hrs:
Photolithograph	y:Oxidation and Photolithography, Ten step patterning proce	ss, Photoresists,
	es of photoresists, Storage and control of photoresists, photo maski	ng process, Hard
	spect, Dry etching Wet etching, resist stripping.	
UNIT - III		Lecture Hrs:
	Implantation: Doping and depositions: Diffusion process steps, d	eposition, Drive-
	implantation-1, Ion implantation-2.	
UNIT - IV		Lecture Hrs:
	s and Growth: Metallization, CVD basics, CVD process steps, Lo	
	enhanced CVD systems, Vapour phase epitaxy, molecular beam epi	
UNIT - V		Lecture Hrs:
•	rules and Scaling, BICMOS ICs: Choice of transistor types,	PNP transistors,
Resistors, capaci		
	characteristics, package functions, package operations.	_
Textbooks:	. M. 1' 61' .' M.C. H'll 1007	
	t, Microchip fabrication, McGraw Hill, 1997.	4.1
	, Deal, M.D. and Griffin, P.B., "Silicon VLSI Technology: Fundam	entais,
Reference Book	odeling", 3rd Ed., Prentice-Hall, 2000.	
	d S.M. Sze, ULSI technology, McGraw Hill, 2000	
	VLSI Fabrication principles, John Wiley and Sons, NY, 1994	
3. S.M. Sze, VLS	SI technology, McGraw-Hill Book company, NY, 1988	



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

21D57103b Program Elective – I 3 0 0 Semester I		Course Code	NANOMATERIALS AND NANOTECHNOLOGY	L	T	P	C	
Semester I		21D57103b	Program Elective – I	3	0	0	3	
Schester	Ī		Semester	Ī				

Course Objectives:

- To understand the basic idea behind the design and fabrication of nano scale systems.
- To understand and frmulate new engineering solutions for current problems and technologies for future applications.
- To acquire knowledge on the operation of fabrication and characterization devices to achieve precisely designed systems.

Course Outcomes (CO): Student will be able to

- Understand the basic science behind the design and fabrication of nano scale systems.
- Understand and formulate new engineering solutions for current problems and competing technologies for future applications.
- Make inter disciplinary projects applicable to wide areas by clearing and fixing the boundaries in system development.
- Gather detailed knowledge of the operation of fabrication and characterization devices to achieve precisely designed systems.

UNIT - I Lecture Hrs:

Introduction of nano materials and nanotechnologies, Features of nanostructures, Applications of nano materials and technologies. Nano dimensional Materials 0D, 1D, 2D structures – Size Effects – Fraction of Surface Atoms –Specific Surface Energy and Surface Stress – Effect on the Lattice Parameter – Phonon Density of States – the General Methods available for the Synthesis of Nanostructures – precipitate – reactive– hydrothermal/solvo thermal methods – suitability of such methods for scaling – potential Uses.

UNIT - II Lecture Hrs:

Fundamentals of nanomaterials, Classification, Zero-dimensional nanomaterials, One-dimensional nanomaterials, Two-dimensional nano materials, three dimensional nanomaterials. Low Dimensional Nanomaterials and its Applications, Synthesis, Properties and applications of Low Dimensional Carbon-Related Nanomaterials.

UNIT - III Lecture Hrs:

Micro- and Nanolithography Techniques, Emerging Applications, Introduction to Micro electro mechanical Systems (MEMS), Advantages and Challenges of MEMS, Fabrication Technologies, Surface Micromachining, Bulk Micromachining, Molding. Introduction to Nano Phonics.

UNIT - IV Lecture Hrs:

Introduction, Synthesis of CNTs - Arc-discharge, Laser-ablation, Catalytic growth, Growth mechanisms of CNT's - Multi-walled nanotubes, Single-walled nano tubes Optical properties of CNT's, Electrical transport in perfect nanotubes, Applications as case studies. Synthesis and Applications of CNTs.

UNIT - V Lecture Hrs:

Ferroelectric materials, coating, molecular electronics and Nano electronics, biological and environmental, membrane based application, polymer based application.

Textbooks:

- 1. Kenneth J.Klabunde and Ryan M.Richards, "Nanoscale Materials in Chemistry", 2ndedition, John Wiley and Sons, 2009.
- 2. I Gusev and A Rempel, "Nanocrystalline Materials", Cambridge International Science Publishing, 1stIndian edition by Viva Books Pvt. Ltd. 2008.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

3. B.S.Murty,P.Shankar,Baldev Raj, B.B.Rath, James Murday, "Nanoscience and Nanotechnology", Tata McGrawHill Education 2012.

- 1. Digital Integrated Circuit Design Ken Martin, Oxford University Press, 2011.
- 2. Digital Integrated Circuits A Design Perspective, Jan M.Rabaey, AnantChandrakasan, Borvivoje Nikolic, 2nd Edition, PHI.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	CAD FOR VLSI	L	Т	P	C
21D57103c	Program Elective – I	3	0	0	3
21D37103C	Semester	3		[[<u> </u>
	Semester				
Course Objectiv	ves:				
	stand the various phases of CAD for digital electronic systems,	from	digi	tal lo	gic
	n to physical design, including test and verification.	0111	- G G		810
	nstrate knowledge and understanding of fundamental concepts	in (CAD	and	to
	capability for CAD tool development and enhancement.				
	the application of fundamentals of VLSI technologies				
_	ize the implemented design for area, timing and power by a	ipply	ing	suita	ble
constraint		11 2	Ü		
Course Outcome	es (CO): Student will be able to				
Establish	comprehensive understanding of the various phases of C	AD	for	dig	ital
electronic	systems, from digital logic simulation to physical design, in	clud	ing 1	test a	and
verification	on.				
 Demonstr 	ate knowledge and understanding of fundamental concepts in CAL) and	l to e	establ	ish
capability	for CAD tool development and enhancement.				
Practice the second of th	he application of fundamentals of VLSI technologies				
Optimize	the implemented design for area, timing and power by applying sui	table	con	strair	ıts.
UNIT - I				Hrs:	
	LSI Design Cycle, New Trends in VLSI Design Cycle, Physical De	sign	Cyc	le, N	ew
	al Design Cycle, Design Styles, System Packaging Styles.				
UNIT - II				Hrs:	
_	artitioning, Pin Assignment and Placement: Partitioning - Prob			ıulati	on,
Classification of	Partitioning algorithms, Kernighan-Lin Algorithm, Simulated Anne	aling	g.		
UNIT - III		Lea	cture	Hrs:	
Floor Planning	:Floor Planning – Problem formulation, Classification of floor plan	ning	g algo	orith	ms,
	floor planning, Rectangular Dualization, Pin Assignment - Prob	lem	form	ıulati	on,
	pin assignment algorithms, General and channel Pin assignments.				
UNIT - IV				Hrs:	
	Routing: Placement–Problem formulation, Classification of place	men	t alg	orithi	ms,
	d placement algorithms.	~-			
	and Detailed Routing: Global Routing – Problem formulation,				
	algorithms, Maze routing algorithms, Detailed Routing – Problems	em	torn	ıulatı	on,
	routing algorithms, Single layer routing algorithms.	Τ.	- 4	T T	
UNIT - V	Automation of FPGAs and MCMs: FPGA Technologies, Physical Research			Hrs:	
			•	_	
	titioning, Routing – Routing Algorithm for the Non-Segmented he Segmented Model; Introduction to MCM Technologies, MCM				_
Cycle.	ne beginemed wioder, introduction to wiew reciniologies, wiew	1 1119	sical	Des	ıgıı
Textbooks:					
	for VLSI Physical Design Automation by Naveed Shervani,	3rdFc	lition	20	05
1. Algoridinis	north and Edding	, 1:0	ııııUII	, ∠∪	υ,,

2. CMOS Digital Integrated Circuits Analysis and Design - Sung-Mo Kang, Yusuf Leblebici,

Springer International Edition.

TMH, 3rd Ed., 2011.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

- 1. VLSI Physical Design Automation-Theory and Practice by Sadiq M Sait, Habib Youssef, World Scientific.
- 2. Algorithms for VLSI Design Automation, S. H. Gerez, 1999, Wiley student Edition, John Wiley and Sons (Asia) Pvt. Ltd.
- 3. VLSI Physical Design Automation by Sung Kyu Lim, Springer International Edition



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	DEVICE MODELLING	L	T	P	С
21D57104a	Program Elective – II	3	0	0	3
	Semester			I	
Course Objectiv					
	tand the physics of 2-terminal MOS operation and its characteristic				
 To unders 	tand the physics of 4-terminal MOSFET operation and its character	istic	cs.		
	e the SOI MOSFET electrical characteristics.				
	es (CO): Student will be able to				
	d the physics of 2-terminal MOS operation and its characteristics				
 Understan 	d the physics of 4-terminal MOSFET operation and its characterist	ics.			
	he SOI MOSFET electrical characteristics.				
UNIT - I		Le	cture	Hrs:	
2-terminal MOS	device: threshold voltage modelling (ideal case as well as consider	ing	the e	ffect	s of
Qf, Φms and Dit.).				
UNIT - II				Hrs:	
	cs (ideal case as well as taking into account the effects of Qf, Φn				
_	agnostic tool (measurement of non-uniform doping profile, estimate	atior	of of	Qf, 4	ms
and Dit)					
UNIT - III				Hrs:	
	FET: threshold voltage (considering the substrate bias); abov	e tl	nresh	old	I-V
	E level 1,2,3 and 4).				
UNIT - IV				Hrs:	
	rrent model; scaling; effect of threshold tailoring implant (analyti				
	e using box approximation); buried channel MOSFET. Short cha	nne	I, D	IBL :	and
	ects; small signal analysis of MOSFETs (Meyer's model)				
UNIT - V				Hrs:	
	Basic structure; threshold voltage modelling Advanced topics:	ho	t ca	rriers	ın
	Ms; CCDs; high-K gate dielectrics.				
Textbooks:	· · · · · · · · · · · · · · · · · · ·				
	sics of Semiconductor Devices, (2e), Wiley Eastern, 1981.	D4.a. '	T 4.1		
	Fundamentals of Nanotransistors, World Scientific Publishing Co	rie.	Lla		
2017.	,				
Reference Books		07			
	Operation and Modelling of the MOS Transistor, McGraw-Hill, 19	٥/.			
	t-carrier Effects in MOS Trasistors, Academic Press, 1995.				
5. J. P. Collinge,	FinFETs and Other Multi-Gate Transistors," Springer. 2009				



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	FPGA ARCHITECTURES AND APPLICATIONS	L	C						
21D57104b	Program Elective – II	3	3 0 0						
Semester I									
Course Objectives:									
 To acquire l 	knowledge about various architectures and device technologies of	`PLI	O's.						

- To comprehend FPGA Architectures.
- To analyze System level Design and their application for Combinational and Sequential Circuits.
- To familiarize with Anti-Fuse Programmed FPGAs.
- To apply knowledge of this subject for various design applications.

Course Outcomes (CO): Student will be able to

- Acquire knowledge about various architectures and device technologies of PLD's.
- Comprehend FPGA Architectures.
- Analyze System level Design and their application for Combinational and Sequential Circuits.
- Familiarize with Anti-Fuse Programmed FPGAs.
- Apply knowledge of this subject for various design applications.

UNIT - I Lecture Hrs: Introduction to Programmable Logic Devices: Introduction, Simple Programmable Logic Devices - Read Only Memories, Programmable Logic Arrays, Programmable Array Logic, Programmable Logic Devices/Generic Array Logic; Complex Programmable Logic Devices-Architecture of Xilinx

Cool Runner XCR3064XL CPLD, CPLD Implementation of a Parallel Adder with Accumulation. UNIT - II Lecture Hrs: **Field Programmable Gate Arrays** Field Programmable Gate Arrays: Organization of FPGAs, FPGA Programming Technologies,

Programmable Logic Block Architectures, Programmable Interconnects, and Programmable I/O blocks in FPGAs, Dedicated Specialized Components of FPGAs, and Applications of FPGAs.

SRAM Programmable FPGAs:Introduction, Programming Technology, Device Architecture, the Xilinx XC2000, XC3000 and XC4000 Architectures.

UNIT - IV Lecture Hrs:

Anti-Fuse Programmed FPGAs:Introduction, Programming Technology, Device Architecture, The Actel ACT1, ACT2 and ACT3 Architectures.

UNIT - V Lecture Hrs:

Design Applications: General Design Issues, Counter Examples, A Fast Video Controller, A Position Tracker for a Robot Manipulator, A Fast DMA Controller, Designing Counters with ACT devices, Designing Adders and Accumulators with the ACT Architecture

Textbooks:

- Field Programmable Gate Array Technology Stephen M. Trimberger, Springer International
- Digital Systems Design Charles H. Roth Jr, LizyKurian John, Cengage Learning.

- 1. Field Programmable Gate Arrays-John V.Oldfield, Richard C.Dorf, Wiley India.
- 2. Digital Design Using Field Programmable Gate Arrays Pak K. Chan/SamihaMourad, Pearson Low Price Edition.
- 3. Digital Systems Design with FPGAs and CPLDs-Ian Grout, Elsevier, Newnes.
- FPGA based System Design-Wayne Wolf, Prentice Hall Modern Semiconductor Design Series.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	ASIC DESIGN	L	T	P	C
21D57104c	Program Elective – II	3	0	0	3
	Semester]	[
Course Objective	es:				
 To underst 	and different types of ASICs and their libraries.				
 To underst 	and about programmable ASICs, I/O modules and their interconne	cts.			
 To familia 	arize different methods of software ASIC design their simulat	tion,	test	ing a	and
construction	on of ASICs.			_	
Course Outcome	s (CO): Student will be able to				
Understand	d different types of ASICs and their libraries.				
	d about programmable ASICs, I/O modules and their interconnects				
	e different methods of software ASIC design their simulati		testi	ng a	and
	on of ASICs.	,		υ	
UNIT - I		Leo	cture	Hrs:	
Introduction to	ASICs: Types of ASICs, Design Flow, Case Study, Economics	of A	ASIC	s, AS	SIC
	ansistors as resistors, Transistor Parasitic Capacitance, Logical Eff				
	rchitecture, Gate-Array Design, Standard Cell Design, Data Path C				
UNIT - II	•	Leo	cture	Hrs:	
Programmable A	SICs and Programmable ASIC Logic Cells: The Anti fuse, Stat	ic R	am, l	EPR(DΜ
and EEPROM Te	chnology, Practical Issues, Specifications, PREDP Benchmarks, Fl	PGA	Eco	nomi	ics,
Actel ACT, Xilinx	LCA, Altera Flex, Altera Max.				
UNIT - III		Le	cture	Hrs:	
	terconnects & Programmable ASIC Design Software: DC Ou				
	ut, Clock input, Power input, Xilinx I/O block, Other I/O Cells, A				
	D, Altera Max 5000 and 7000, Altera Max 9000, Altera FLEX,	Des	ign S	ystei	ms,
·	The Half gate ASIC.				
UNIT - IV				Hrs:	
- C	n Entry and Logic Synthesis: Schematic Entry, Low level De	_			-
	F, A logic synthesis example, A Comparator/MUX, Inside a Lo				
	bi Decoder, Verilog and Logic synthesis, VHDL and Logic Synthesis				
_	is, Memory Synthesis, The Engine Controller, Performance D	rive	n Sy	nthe	sis,
Optimization of th	e viterbi decoder.				
UNIT - V			cture		
	and ASIC Construction: Types of Simulation, The Comparator				
•	ow Logic Simulation Works, Cell Models, Delay Models, Static		_	•	
Formal Verification, Switch Level Simulation, Transistor Level Simulation, The importance of test,					
	est, Faults, Faults Simulation, Automatic Test Pattern Generator, S				
_	le test Example, Physical Design, CAD Tools, System Partition	ning	, Est	ımat	ıng
ASIC Size, Power	er Dissipation, FPGA Partitioning, Partitioning Methods				

Reference Books:

Textbooks:

1. HimanshuBhatnagar, "Advanced ASIC Chip Synthesis using Synopsis Design Compiler", 2nd Edition, Kluwer Academic, 2001.

1. Michael John Sebastian Smith, "Application Specific Integrated Circuits", Pearson Education,

2. L.J.Herbst, "Integrated Circuit Engineering", Oxford Science Publications, 1996.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	CMOS ANALOG IC DESIGN LAB	L	T	P	С	
21D57105		0	0	4	2	
	Semester		I			

Course Objectives:

- To explain the VLSI Design Methodologies using VLSI design tool.
- To grasp the significance of various CMOS analog circuits in full-custom IC Design flow
- To explain the Physical Verification in Layout Design
- To fully appreciate the design and analyze of analog and mixed signal simulation
- To grasp the Significance of Pre-Layout Simulation and Post-Layout Simulation

Course Outcomes (CO):

- Explain the VLSI Design Methodologies using VLSI design tool.
- Grasp the significance of various CMOS analog circuits in full-custom IC Design flow
- Explain the Physical Verification in Layout Design
- Fully appreciate the design and analyze of analog and mixed signal simulation
- Grasp the Significance of Pre-Layout Simulation and Post-Layout Simulation

List of Experiments:

- The students are required to design and implement any **TEN** Experiments using CMOS 130nm Technology.
- The students are required to implement LAYOUTS of any **SIX** Experiments using CMOS 130nm Technology and Compare the results with Pre-Layout Simulation.
- 1. MOS Device Characterization and parametric analysis
- 2. Common Source Amplifier
- 3. Common Source Amplifier with source degeneration
- 4. Cascode amplifier
- 5. Simple current mirror
- 6. Cascode current mirror.
- 7. Wilson current mirror.
- 8. Differential Amplifier
- 9. Operational Amplifier
- 10. Sample and Hold Circuit
- 11. Direct-conversion ADC
- 12. R-2R Ladder Type DAC

Lab Requirements:

Software:

Mentor Graphics – Pyxis Schematic, IC Station, Calibre, ELDO Simulator

Hardware:

Personal Computer with necessary peripherals, configuration and operating System.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	CMOS DIGITAL IC DESIGN LAB	L	T	P	C	
21D57106		0	0	4	2	
	Semester		I			

Course Objectives:

- To explain the VLSI Design Methodologies using any VLSI design tool.
- To grasp the significance of various design logic Circuits in full-custom IC Design.
- To explain the Physical Verification in Layout Extraction.
- To fully appreciate the design and analyze of CMOS Digital Circuits.
- To grasp the Significance of Pre-Layout Simulation and Post-Layout Simulation.

Course Outcomes (CO):

- Explain the VLSI Design Methodologies using any VLSI design tool.
- Grasp the significance of various design logic Circuits in full-custom IC Design.
- Explain the Physical Verification in Layout Extraction.
- Fully appreciate the design and analyze of CMOS Digital Circuits.

Grasp the Significance of Pre-Layout Simulation and Post-Layout Simulation.

List of Experiments:

The students are required to design and implement the Circuit and Layout of any **TEN** Experiments using CMOS 130nm Technology.

- 1. Inverter Characteristics.
- 2. NAND and NOR Gate
- 3. XOR and XNOR Gate
- 4. 2:1 Multiplexer
- 5. Full Adder
- 6. RS-Latch
- 7. Clock Divider
- 8. JK-Flip Flop
- 9. Synchronous Counter
- 10. Asynchronous Counter
- 11.Static RAM Cell
- 12. Dynamic Logic Circuits
- 13. Linear Feedback Shift Register

Lab Requirements:

Software:

Mentor Graphics Tool/ Cadence/ Synopsys/Industry Equivalent Standard Software

Hardware

Personal Computer with necessary peripherals, configuration and operating System.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	RESEARCH METHODOLOGY AND IPR	L	T	P	С
21DRM101		2	0	0	2
<u>.</u>	Semester			Ι	
Course Objective	S:				
· · · · · · · · · · · · · · · · · · ·	appropriate research problem in their interesting domain.				
 Understan 	d ethical issues understand the Preparation of a research project th	esis rep	ort.		
 Understan 	d the Preparation of a research project thesis report	_			
• Understan	d the law of patent and copyrights.				

Course Outcomes (CO): Student will be able to

Understand the Adequate knowledge on IPR

- Analyze research related information
- Follow research ethics
- Understand that today's world is controlled by Computer, Information Technology, but tomorrow world will be ruled by ideas, concept, and creativity.
- Understanding that when IPR would take such important place in growth of individuals & nation, it is needless to emphasis the need of information about Intellectual Property Right to be promoted among students in general & engineering in particular.
- Understand that IPR protection provides an incentive to inventors for further research work and investment in R & D, which leads to creation of new and better products, and in turn brings about, economic growth and social benefits.

UNIT - I Lecture Hrs:

Meaning of research problem, Sources of research problem, Criteria Characteristics of a good research problem, Errors in selecting a research problem, scope, and objectives of research problem. Approaches of investigation of solutions for research problem, data collection, analysis, interpretation, Necessary instrumentations

UNIT - II Lecture Hrs:

Effective literature studies approaches, analysis Plagiarism, Research ethics, Effective technical writing, how to write report, Paper Developing a Research Proposal, Format of research proposal, a presentation and assessment by a review committee.

UNIT - III Lecture Hrs:

Nature of Intellectual Property: Patents, Designs, Trade and Copyright. Process of Patenting and Development: technological research, innovation, patenting, development. International Scenario: International cooperation on Intellectual Property. Procedure for grants of patents, Patenting under PCT.

UNIT - IV Lecture Hrs:

Patent Rights: Scope of Patent Rights. Licensing and transfer of technology. Patent information and databases. Geographical Indications.

UNIT - V

New Developments in IPR: Administration of Patent System. New developments in IPR; IPR of Biological Systems, Computer Software etc. Traditional knowledge Case Studies, IPR and IITs.

Textbooks:

- 1. Stuart Melville and Wayne Goddard, "Research methodology: an introduction for science & engineering students"
- 2. Wayne Goddard and Stuart Melville, "Research Methodology: An Introduction"

- 1. Ranjit Kumar, 2nd Edition, "Research Methodology: A Step by Step Guide for beginners"
- 2. Halbert, "Resisting Intellectual Property", Taylor & Drancis Ltd ,2007.
- 3. Mayall, "Industrial Design", McGraw Hill, 1992.
- 4. Niebel, "Product Design", McGraw Hill, 1974.
- 5. Asimov, "Introduction to Design", Prentice Hall, 1962.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

6. Robert P. Merges, Peter S. Menell, Mark A. Lemley, "Intellectual Property in New Technological Age", 2016.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	CMOS MIXED SIGNAL IC DESIGN	L	T	P	C
21D57201		3	0	0	3
	Semester		I	I	
Course Objecti	ves:				
 To demo 	nstrate first order filter with least interference				
 To exten 	d the concept of phase locked loop for designing PLL applicatio	n w	ith m	inim	um
	considering non ideal effects.				
•	n different A/D, D/A, modulators, demodulators and different fil	lter	for r	eal ti	me
application					
	es (CO): Student will be able to				
	rate first order filter with least interference				
	ne concept of phase locked loop for designing PLL application wit	h m	inimı	ım ji	tter
-	lering non ideal effects.				
	lifferent A/D, D/A, modulators, demodulators and different filt	er f	or re	eal ti	me
application	ons				
UNIT - I			cture		
	citor Circuits: Introduction to Switched Capacitor circuits- basic				
	Analysis, Non-ideal effects in switched capacitor circuits, Sw	/itch	ed c	apacı	itor
	order filters, Switch sharing, biquad filters.	т		T T	
UNIT – II			cture		,
	oop (PLL): Basic PLL topology, Dynamics of simple PLL, Cha	_	-		
•	n, Phase/Frequency detector and charge pump, Basic charge pump		L, N	on-10	ieai
UNIT - III	PFD/CP non-idealities, Jitter in PLLs, Delay locked loops, applicati		cture	Hree	
	: Fundamentals DC and dynamic specifications, Quantization no				ate
	Decoder based converters, Binary-Scaled converters, Thermometer				
Hybrid converte	· · · · · · · · · · · · · · · · · · ·	000		1 / 01 (010,
UNIT - IV		Leo	cture	Hrs:	
	rters: Nyquist Rate A/D Converters Successive approximation				ash
	-step A/D converters, Interpolating A/D converters, Folding				
	onverters, Sigma Delta A/D coverters, Time- interleaved converters.				ŕ
UNIT - V			cture	Hrs:	
Oversampling	Converters: Noise shaping modulators, Decimating filters and int	erpo	lating	g filte	ers,
Higher order mo	dulators, Delta sigma modulators with multi bit quantizers, Delta sig	gma	D/A		
Textbooks:					
1. Design of Ana	alog CMOS Integrated Circuits- BehzadRazavi, TMH Edition, 2002				
	g Circuit Design - Philip E. Allen and Douglas R. Holberg, Oxford	Uni	versit	y Pre	ess,
	cond Edition/Indian Edition, 2010.				
	ated Circuit Design- David A. Johns, Ken Martin, Wiley Student Ed	litio	n, 20	13	
Reference Book				_	
	rated Analog-to- Digital and Digital-to-Analog converters- Rudy	√an	De F	lassc	he,
	ic Publishers, 2003	•	0.5		
	Delta-Sigma Data converters-Richard Schreier, Wiley Inter science	, 20	05.		
3. CMOS Mixed	-Signal Circuit Design - R. Jacob Baker, Wiley Interscience,2009				



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Objectives: To understand relation between automation algorithms and constraints posed by VLSI technology. To adopt algorithms to meet critical design parameters. To design area efficient logics by employing different routing algorithms and shape functions. To simulate and synthesis different combinational and sequential logics. Course Outcomes (CO): Student will be able to
Course Objectives: • To understand relation between automation algorithms and constraints posed by VLSI technology. • To adopt algorithms to meet critical design parameters. • To design area efficient logics by employing different routing algorithms and shape functions. • To simulate and synthesis different combinational and sequential logics. Course Outcomes (CO): Student will be able to • Understand relation between automation algorithms and constraints posed by VLSI technology. • Adopt algorithms to meet critical design parameters. • Design area efficient logics by employing different routing algorithms and shape functions. • Simulate and synthesis different combinational and sequential logics. UNIT - I UNIT - II Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lequal
To understand relation between automation algorithms and constraints posed by VLSI technology. To adopt algorithms to meet critical design parameters. To design area efficient logics by employing different routing algorithms and shape functions. To simulate and synthesis different combinational and sequential logics. Course Outcomes (CO): Student will be able to Understand relation between automation algorithms and constraints posed by VLSI technology. Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis, ROBDD principles, implementation, construction of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998.
 To understand relation between automation algorithms and constraints posed by VLSI technology. To adopt algorithms to meet critical design parameters. To design area efficient logics by employing different routing algorithms and shape functions. To simulate and synthesis different combinational and sequential logics. Course Outcomes (CO): Student will be able to Understand relation between automation algorithms and constraints posed by VLSI technology. Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. Luyit - II Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis, ROBDD principles, implementation, construction and manipulation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High-Level Synthesis: Hardware model for high level synt
technology. To adopt algorithms to meet critical design parameters. To design area efficient logics by employing different routing algorithms and shape functions. To simulate and synthesis different combinational and sequential logics. Course Outcomes (CO): Student will be able to Understand relation between automation algorithms and constraints posed by VLSI technology. Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis. ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Design Automation, John Wiley, 1999
 To adopt algorithms to meet critical design parameters. To design area efficient logics by employing different routing algorithms and shape functions. To simulate and synthesis different combinational and sequential logics. Understand relation between automation algorithms and constraints posed by VLSI technology. Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Al
 To design area efficient logics by employing different routing algorithms and shape functions. To simulate and synthesis different combinational and sequential logics. Course Outcomes (CO): Student will be able to Understand relation between automation algorithms and constraints posed by VLSI technology. Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis. ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Aspects of assignment, High level transformations. Textbooks: L. S. H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. N.
To simulate and synthesis different combinational and sequential logics. Course Outcomes (CO): Student will be able to Understand relation between automation algorithms and constraints posed by VLSI technology. Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis. ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Outse Outcomes (CO): Student will be able to Understand relation between automation algorithms and constraints posed by VLSI technology. Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis. ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Understand relation between automation algorithms and constraints posed by VLSI technology. Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I
Adopt algorithms to meet critical design parameters. Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Design area efficient logics by employing different routing algorithms and shape functions. Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Design Automation, (3/e), Kluwer, 1999.
Simulate and synthesis different combinational and sequential logics. UNIT - I Lecture Hrs: VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Lecture Hrs: Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II
VLSI Design Automation Tools: Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II
Transistor level design, Layout design, Verification methods, Design management tools. UNIT - II Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III
Layout: Compaction, placement and routing, Design rules, symbolic layout, Applications of compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III
compaction. Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms. UNIT - III
Testbooks: UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
UNIT - III Lecture Hrs: Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Floor planning and routing: Floor planning concepts, Shape functions and floor planning sizing, Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Local routing, Area routing, Channel routing, global routing and its algorithms. UNIT - IV Lecture Hrs: Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
UNIT - IV Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V Lecture Hrs: High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Simulation and Logic Synthesis: Gate level and switch level modeling and simulation, Introduction to combinational logic synthesis, ROBDD principles, implementation, construction and manipulation, Two level logic synthesis. UNIT - V
manipulation, Two level logic synthesis. UNIT - V
UNIT - V High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
High-Level Synthesis: Hardware model for high level synthesis, internal representation of input algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
algorithms, Allocation, assignment and scheduling, scheduling algorithms, Aspects of assignment, High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
High level transformations. Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Textbooks: 1. S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. 2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
 S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
 S.H. Gerez, Algorithms for VLSI Design Automation, John Wiley, 1998. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
2. N.A. Sherwani, Algorithms for VLSI Physical Design Automation, (3/e), Kluwer, 1999.
Reference Books:
1. S.M. Sait, H. Youssef, VLSI Physical Design Automation, World scientific, 1999.
2. M.Sarrafzadeh, Introduction to VLSI Physical Design, McGraw Hill (IE), 1996



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	SoC TESTING AND VERIFICATION	L	T	P	C			
21D57203a	Program Elective – III	3	3					
	Semester	II						
Course Objecti								
To under	erstand the concepts of faults and testing in SoC							
 To impl 	ement the faults using simulation tools							
To analy	yze BIST systems							
	nes (CO): Student will be able to							
 Underst 	and the concepts of faults and testing in SoC							
 Implem 	ent the faults using simulation tools							
Analyze	BIST systems							
UNIT - I		Leo	ture	Hrs:				
	Testing: Testing Philosophy, Role of Testing, Digital and							
	Technology Trends affecting Testing, Types of Testing,							
Defects, Errors	and Faults, Functional Versus Structural Testing, Levels of Fau	lt M	odels	, Sin	gle			
Stuck-at Fault.								
UNIT - II			cture					
	It Simulation: Simulation for Design Verification and Test Eval				ing			
Circuits for Sim	ulation, Algorithms for True-value Simulation, Algorithms for Faul	t Sin	ulati	on.				
UNIT - III		Leo	ture	Hrs:				
Testability Me	asures: SCOAP Controllability and Observablity, High L	evel	Te	stabi	lity			
Measures, Dig	ital DFT and Scan Design: Ad-Hoc DFT Methods, Scan Des	sign,	Part	ial-S	can			
Design, Variation	ons of Scan.							
UNIT - IV		Lec	cture	Hrs:				
Built-In Self-To	est: The Economic Case for BIST, Random Logic BIST: Definition	ns, B	IST I	Proce	ess,			
	ion, Response Compaction, Built-In Logic Block Observers, Test			k, To	est-			
	Systems, Circular Self Test Path System, Memory BIST, Delay Faul	t BIS	ST.					
UNIT - V			cture					
	Standard: Motivation, System Configuration with Boundary Scar							
	ndary Scan Test Instructions, Pin Constraints of the Standard,	Bo	undaı	ry So	can			
	guage: BDSL Description Components, Pin Descriptions.							
Textbooks:								
	ll, V. D. Agrawal, "Essentials of Electronic Testing for Digital, Mo	emor	y and	l Miz	ced			
	cuits", Kluwer Academic Pulishers.							
	ici, M.A.Breuer and A.D Friedman, "Digital Systems and Testab	le D	esign	", Ja	ico			
Publishing Hous								
Reference Bool								
1. P.K. Lala, "D	igital Circuits Testing and Testability", Academic Press.							
<u> </u>								



structures.

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY ANANTAPUR (Established by Govt. of A.P., ACT No.30 of 2008) ANANTHAPURAMU – 515 002 (A.P) INDIA

M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	SEMICONDUCTOR MEMORY DESIGN AND TESTING	L	T	P	C
21D57203b	Program Elective – III	3	0	0	3
	Semester		I	I	
Course Objecti					
	rstand different types of memories, their architectural and d	liffer	ent	pack	ing
•	es of memories.				
	fault models for memory testing.				
•	ze different parameters that lead malfunctioning of memories.				
 To design 	n reliable memories with efficient architecture to improve proc	esse	s tin	nes a	and
power.					
	es (CO): Student will be able to				
	plete knowledge regarding different types of memories, their	archi	tectu	ral a	and
	packing techniques of memories.				
	lt models for memory testing.				
•	different parameters that lead malfunctioning of memories.				
	eliable memories with efficient architecture to improve processes tin				
UNIT - I			ture		
	ss Memory Technologies :SRAM – SRAM Cell structures				
	OS SRAM cell and peripheral circuit operation, Bipolar SRAM to				
	ranced SRAM architectures and technologies, Application specific				
	ology development, CMOS DRAM, DRAM cell theory and advance				
	M, soft error failure in DRAM, Advanced DRAM design a	and	archi	itecti	ıre,
Application spec	Ific DRAM.	т		T T	
UNIT - II			ture		200
Non realestie M	emories , Miaskey Krimis High Vensily Krimi Ekrimi Bibola				ω
PROMS, EPRO	OM, Floating gate EPROM cell, One time programmable EPR	OM	, EE	PRO	M,
PROMS, EPRO EEPROM tech	OM, Floating gate EPROM cell, One time programmable EPR nology and architecture, Non-volatile SRAM, Flash Memoria	OM	, EE	PRO	M,
PROMS, EPRO EEPROM tech EEPROM), adva	OM, Floating gate EPROM cell, One time programmable EPR	es (, EE EPR	PRO OM	M,
PROMS, EPRO EEPROM tech EEPROM), adva UNIT - III	OM, Floating gate EPROM cell, One time programmable EPR nology and architecture, Non-volatile SRAM, Flash Memorianced Flash memory architecture	es (, EE EPR ture	PRO OM Hrs:	M,
PROMS, EPRO EEPROM tech EEPROM), adva UNIT - III Memory Fault	OM, Floating gate EPROM cell, One time programmable EPR mology and architecture, Non-volatile SRAM, Flash Memorianced Flash memory architecture Modeling Testing and Memory Design for Testability and Fault	es (Lec Tole	EPR ture	PRO OM Hrs:	or
PROMS, EPRO EEPROM tech EEPROM), adva UNIT - III Memory Fault : RAM fault mod	OM, Floating gate EPROM cell, One time programmable EPR mology and architecture, Non-volatile SRAM, Flash Memorianced Flash memory architecture Modeling Testing and Memory Design for Testability and Fault deling, Electrical testing, Pseudo Random testing, Megabit DRA	es (Lec Tole M T	EPR ture ranc	PROOM Hrs: e :	on-
PROMS, EPRO EEPROM tech EEPROM), adva UNIT - III Memory Fault : RAM fault mod volatile memory	OM, Floating gate EPROM cell, One time programmable EPR mology and architecture, Non-volatile SRAM, Flash Memorianced Flash memory architecture Modeling Testing and Memory Design for Testability and Fault	es (Lec Tole M T	EPR ture ranc	PROOM Hrs: e :	on-
PROMS, EPRO EEPROM tech EEPROM), adva UNIT - III Memory Fault : RAM fault mod volatile memory	OM, Floating gate EPROM cell, One time programmable EPR mology and architecture, Non-volatile SRAM, Flash Memorianced Flash memory architecture Modeling Testing and Memory Design for Testability and Fault deling, Electrical testing, Pseudo Random testing, Megabit DRAW modeling and testing, IDDQ fault modeling and testing, App	Lec Tole M Tolicat	EPR ture ranc	Hrs: ee: g, ne	on-
PROMS, EPRO EEPROM tech EEPROM), adva UNIT - III Memory Fault RAM fault moo volatile memory memory testing, UNIT - IV	OM, Floating gate EPROM cell, One time programmable EPR mology and architecture, Non-volatile SRAM, Flash Memorianced Flash memory architecture Modeling Testing and Memory Design for Testability and Fault deling, Electrical testing, Pseudo Random testing, Megabit DRAW modeling and testing, IDDQ fault modeling and testing, App	Lec Tole M Tolicat	ture rance estimation	Hrs: e: g, ne speci	on- ific
PROMS, EPRO EEPROM tech EEPROM), adva UNIT - III Memory Fault RAM fault mood volatile memory memory testing, UNIT - IV Semiconductor modes and median	OM, Floating gate EPROM cell, One time programmable EPR mology and architecture, Non-volatile SRAM, Flash Memorianced Flash memory architecture Modeling Testing and Memory Design for Testability and Fault deling, Electrical testing, Pseudo Random testing, Megabit DRAM modeling and testing, IDDQ fault modeling and testing, App RAM fault modeling, BIST techniques for memory.	Lec Tole M Tolicat Lec Sues and	ture rance estimation ture RAM	Hrs: e; g, ne speci	on- ific

UNIT - V Lecture Hrs:

Radiation effects, Single Event Phenomenon (SEP), Radiation Hardening techniques, Radiation Hardening Process and Design Issues, Radiation Hardened Memory characteristics, Radiation Hardness Assurance and Testing, Radiation Dosimetry, Water Level Radiation Testing and Test

Advanced Memory Technologies and High-density Memory Packing Technologies

Ferroelectric RAMs (FRAMs), GaAs FRAMs, Analog memories, magneto resistive RAMs (MRAMs), Experimental memory devices, Memory Hybrids and MCMs (2D), Memory Stacks and MCMs (3D), Memory MCM testing and reliability issues, Memory cards, High Density Memory



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Packaging Future Directions.

Textbooks:

- Semiconductor Memories Technology Ashok K. Sharma, 2002, Wiley.
 Advanced Semiconductor Memories Architecture, Design and Applications Ashok K. Sharma, 2002, Wiley.

Reference Books:

1. Modern Semiconductor Devices for Integrated Circuits – Chenming C Hu, First Edition. Prentice



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code Program Elective - III						
Course Objectives: To understand the basic concepts of MEMS technology and working of MEMS devices. To understand and select different materials for current MEMS devices and competing technologies for future applications. To understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. To analyze the various fabrication techniques in the manufacturing of MEMS Devices. Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices and competing technologies for future applications. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors).MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - II Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding Selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understandining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Sevices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro maters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved i	Course Code	MEMS SYSTEM DESIGN	L	P	C	
Course Objectives: To understand the basic concepts of MEMS technology and working of MEMS devices. To understand and select different materials for current MEMS devices and competing technologies for future applications. To understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. To analyze the various fabrication techniques in the manufacturing of MEMS Devices. Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications. UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - II Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk & Surface Micromachining, Die, Wire & Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD,	21D57203c	Program Elective – III	3	0	0	3
To understand the basic concepts of MEMS technology and working of MEMS devices. To understand and select different materials for current MEMS devices and competing technologies for future applications. To understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. To analyze the various fabrication techniques in the manufacturing of MEMS Devices. Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications. UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piczo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging, Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro		Semester		I	•	
 To understand the basic concepts of MEMS technology and working of MEMS devices and competing technologies for future applications. To understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. To analyze the various fabrication techniques in the manufacturing of MEMS Devices. Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes – 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes – 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging, Understanding selection of Fab processes based on Applications. UNIT - V						
 To understand and select different materials for current MEMS devices and competing technologies for future applications. To understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. To analyze the various fabrication techniques in the manufacturing of MEMS Devices. Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - II Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging, Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro hierters, Ac	Course Objective	es:				
technologies for future applications. To understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. To analyze the various fabrication techniques in the manufacturing of MEMS Devices. Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I	 To underst 	and the basic concepts of MEMS technology and working of MEM	IS d	evice	s.	
To understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. To analyze the various fabrication techniques in the manufacturing of MEMS Devices. Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr., Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - II Lecture Hrs: MEMS Fab Processes – 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes – 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging, Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	 To unders 	tand and select different materials for current MEMS devices	ano	d co	mpet	ing
Methodology. To analyze the various fabrication techniques in the manufacturing of MEMS Devices. Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Povices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro meaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	technologi	es for future applications.				
Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes – 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes – 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging, Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Povices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro mirrors in DMD, Inkjet printer-head, Understanding steps involved in Fabricating above devices.	 To unders 	stand the concepts of fabrication process of MEMS, Design	and	l Pa	ckag	ing
Course Outcomes (CO): Student will be able to Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes – 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes – 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging, Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	Methodolo	ogy.				
Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - II Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	 To analyze 	the various fabrication techniques in the manufacturing of MEMS	Dev	vices.		
Understand the basic concepts of MEMS technology and working of MEMS devices. Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - II Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.						
Understand and select different materials for current MEMS devices and competing technologies for future applications. Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I Lecture Hrs: Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.						
technologies for future applications. • Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. • Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I						
Understand the concepts of fabrication process of MEMS, Design and Packaging Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I			and	l co	mpet	ing
Methodology. Analyze the various fabrication techniques in the manufacturing of MEMS Devices. UNIT - I	-					
NIT - I Lecture Hrs: Lecture Hrs:			anc	l Pa	ckag	ing
UNIT - I Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.		e:				
Introduction to MEMS: Introduction to MEMS & Real world Sensor/Actuator examples (DMD, Air-bag, pressure sensors). MEMS Sensors in Internet of Things (IoT), Bio-Medical Applications UNIT - II	·	e various fabrication techniques in the manufacturing of MEMS D				
UNIT - II Lecture Hrs: MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes - 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.						
WEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III Lecture Hrs: MEMS Fab Processes – 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes – 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.				•		ID,
MEMS Materials and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, Ti, SU8, PMMA, Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III	Air-bag, pressure	sensors).MEMS Sensors in Internet of Things (IoT), Bio-Medical	App	licati	ons	
Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III	UNIT - II		Lec	ture	Hrs:	
Pt); Important properties: Young modulus, Poisson's ratio, density, piezo-resistive coefficients, TCR, Thermal Conductivity, Material Structure. Understanding Selection of materials based on applications. UNIT - III	MEMS Material	s and Their Properties: Materials (eg. Si, SiO2, SiN, Cr, Au, 7	Γi, S	U8, 1	PMN	ĪA,
UNIT - III Lecture Hrs: MEMS Fab Processes – 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth &Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes – 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	Pt); Important pro	perties: Young modulus, Poisson's ratio, density, piezo-resistive c	oeffi	cient	s, TO	CR,
MEMS Fab Processes — 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes — 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	Thermal Conduc	ctivity, Material Structure. Understanding Selection of material	erials	s ba	sed	on
MEMS Fab Processes – 1: Understanding MEMS Processes & Process parameters for: Cleaning, Growth & Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV Lecture Hrs: MEMS Fab Processes – 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk Surface Micromachining, Die, Wire Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	applications.					
Growth &Deposition, Ion Implantation & Diffusion, Annealing, Lithography. Understanding selection of Fab processes based on Applications. UNIT - IV	UNIT - III		Lec	ture	Hrs:	
selection of Fab processes based on Applications. UNIT - IV MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	MEMS Fab Pro	cesses – 1: Understanding MEMS Processes & Process paramete	rs fo	or: C	leani	ng,
UNIT - IV Lecture Hrs: MEMS Fab Processes - 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk Surface Micromachining, Die, Wire Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	Growth &Deposit	ition, Ion Implantation & Diffusion, Annealing, Lithography	. U	nders	stand	ing
MEMS Fab Processes – 2: Understanding MEMS Processes & Process parameters for: Wet & Dry etching, Bulk Surface Micromachining, Die, Wire Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	selection of Fab p	rocesses based on Applications.				
etching, Bulk& Surface Micromachining, Die, Wire& Wafer Bonding, Dicing, Packaging. Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.						
Understanding selection of Fab processes based on Applications. UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.						
UNIT - V Lecture Hrs: MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.	etching, Bulk&	Surface Micromachining, Die, Wire& Wafer Bonding, Die	ing,	Pac	ckagi	ng.
MEMS Devices: Architecture, working and basic quantitative behaviour of Cantilevers, Micro heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.		ection of Fab processes based on Applications.				
heaters, Accelerometers, Pressure Sensors, Micro mirrors in DMD, Inkjet printer-head. Understanding steps involved in Fabricating above devices.						
Understanding steps involved in Fabricating above devices.						
· · · · · · · · · · · · · · · · · · ·			jet	print	er-he	ad.
The state of the s	•	ps involved in Fabricating above devices.				
Textbooks:	Textbooks:					

- 1. An Introduction to Micro electromechanical Systems Engineering; 2nd Edition by N.Maluf, K Williams; Publisher: Artech House Inc
- 2. Practical MEMS by Ville Kaajakari; Publisher: Small Gear Publishing
- 3. Micro system Design by S. Senturia; Publisher: Springer

Reference Books:

1. Analysis and Design Principles of MEMS Devices – Minhang Bao; Publisher: Elsevier Science.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

- 2. Fundamentals of Micro fabrication by M. Madou; Publisher:CRC Press; 2ndedition
- 3. Micro Electro Mechanical System Design by J. Allen; Publisher: CRC Press
- 4. Micro machined Transducers Sourcebook by G. Kovacs; Publisher: McGraw-Hill



Engineering. **Reference Books:**

Press, 2011.

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY ANANTAPUR (Established by Govt. of A.P., ACT No.30 of 2008) ANANTHAPURAMU - 515 002 (A.P) INDIA

M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	LOW POWER VLSI DESIGN	L	T	P	C
21D57204a	Program Elective – IV	3	0	0	3
	Semester		I	I	
Course Objecti	ves:				
 To under 	stand the concepts of velocity saturation, Impact Ionization and Hot	Elec	tron	Effec	et
 To imple 	ment Low power design approaches for system level and circuit level	el me	easur	es.	
 To design 	n low power adders, multipliers and memories for efficient design of	f sysi	tems.		
Course Outcom	nes (CO): Student will be able to				
Understa	nd the concepts of velocity saturation, Impact Ionization and Hot Ele	ectro	n Eff	fect	
 Impleme 	nt Low power design approaches for system level and circuit level n	neası	ıres.		
_	ow power adders, multipliers and memories for efficient design of sy				
UNIT - I			ture	Hrs:	
Fundamentals:	Need for Low Power Circuit Design, Sources of Power Dissipar	tion	– Sta	atic a	and
	Dissipation, Short Circuit Power Dissipation, Glitching Power D				
Channel Effects	-Drain Induced Barrier Lowering and Punch Through, Surface Sca	atteri	ing, V	Veloc	city
Saturation, Impa	ct Ionization, Hot Electron Effect.				•
UNIT - II		Lec	ture	Hrs:	
Low-Power Des	sign Approaches: Low-Power Design through Voltage Scaling – V	TCN	IOS	circu	its,
MTCMOS circu	uits, Architectural Level Approach -Pipelining and Paral	llel	Pro	ocess	ing
Approaches. S	witched Capacitance Minimization Approaches: System Level N	Meas	sures,	Circ	cuit
	Mask level Measures.				
UNIT - III			ture		
	,		OS		
	Ripple Carry Adders, Carry Look Ahead Adders, Carry Select Ad				
	oltage Low-Power Design Techniques – Trends of Technology and	nd P	ower	Sup	ply
	oltage Low-Power Logic Styles.	-			
UNIT - IV			ture		
_	Low-Power Multipliers: Introduction, Overview of Multiplic			_	
_	tectures, Braun Multiplier, Baugh Wooley Multiplier, Booth Multip	lier,	Intro	duct	ion
to Wallace Tree	Multiplier.	Ŧ		T T	
UNIT - V	D M ' D ' CDOM I D DOM'T I I		ture		
	ow-Power Memories: Basics of ROM, Low-Power ROM Technology				
	nt of ROMs, Basics of SRAM, Memory Cell, Precharge and Equ				
	AM Technologies, Basics of DRAM, Self-Refresh Circuit, Fundam	uture	116	aid 8	ıııu
Development of	DIAMI.				
Textbooks:	l Integrated Circuits – Analysis and Design – Sung-Mo Kang,	Viici	ıf I	hlah	ici
TMH, 2011.	i integrated Circuits – Anarysis and Design – Sung-Wo Kang,	1 ust	ai LC	LOICO	101,
· ·	Low-Power VLSI Subsystems – Kiat-Seng Yeo, Kaushik Roy, T	мн	Prof	essin	nal
2. Low-voilage	Low-1 ower vest subsystems - Klat-seng 160, Kaushik Koy, 1	14111	1101	C9910	mai

1. Introduction to VLSI Systems: A Logic, Circuit and System Perspective – Ming-BO Lin, CRC

3. Low Power CMOS VLSI Circuit Design - Kaushik Roy, Sharat C. Prasad, John Wiley & Sons, 2000.

2.Low Power CMOS Design – AnanthaChandrakasan, IEEE Press/Wiley International, 1998.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	IOT AND ITS APPLICATIONS	L	T	P	C
21D57204b	Program Elective – IV	3	0	0	3
	Semester		I	I	
Course Objective	es:				
To apply the second control of the seco	he Knowledge in IOT Technologies and Data management.				
To determ	ine the values chains Perspective of M2M to IOT.				
To implem	nent the state of the Architecture of an IOT.				
To compar	re IOT Applications in Industrial & real world.				
To demons	strate knowledge and understand the security and ethical issues of	an IC	T.		
	s (CO): Student will be able to				
Apply the	Knowledge in IOT Technologies and Data management.				
	the values chains Perspective of M2M to IOT.				
	the state of the Architecture of an IOT.				
•	OT Applications in Industrial & real world.				
_	ate knowledge and understand the security and ethical issues of an	IOT.			
UNIT - I	Ţ		ture	Hrs:	
Fundamentals	of IoT: Evolution of Internet of Things, Enabling Te	chno	logie	es, l	To
Architectures, one	M2M, IoT World Forum (IoTWF) and Alternative IoT models	, Siı	nplif	ied I	To
Architecture and	Core IoT Functional Stack, Fog, Edge and Cloud in IoT, Function	onal	blocl	s of	an
IoT ecosystem, Se	ensors, Actuators, Smart Objects and Connecting Smart Objects.				
	view: Overview of IoT supported Hardware platforms such as: Ra	ispbe	erry p	i, AF	RM
	, Arduino and Intel Galileo boards.				
UNIT - II			ture		
	TAccess Technologies: Physical and MAC layers, topology and		•		
	4g, 802.15.4e, 1901.2a, 802.11ah and Lora WAN, Network La				
	es and Constrained Networks, Optimizing IP for IoT: From 6L				
	Power and Lossy Networks, Application Transport Methods: Suj	pervi	sory	Cont	roi
UNIT - III	ion, Application Layer Protocols: CoAP and MQTT.	Τ	4	T T	
	elopment: Design Methodology, Embedded computing logic,		ture		1
	IoT system building blocks, Arduino, Board details, IDE progran				
	Raspberry Pi with Python Programming.	шшп	g, Ka	ispoc	11 y
UNIT - IV	Raspocity 11 with 1 ython 1 rogramming.	Lec	ture	Hrc	
	nd Supporting Services: Structured Vs Unstructured Data and D				Vs
_	e of Machine Learning – No SQL Databases, Hadoop Ecosysten				
	ge Streaming Analytics and Network Analytics, Xively Cloud for	_			
	ework, Django, AWS for IoT, System Management with NETCON				
UNIT - V			ture		
Case Studies/Ind	ustrial Applications: IoT applications in home, infrastructures, but				ity,
	appliances, other IoT electronic equipments. Use of Big Data and				
IoT, Industry 4.0	concepts. Sensors and sensor Node and interfacing using any	Emb	edde	d tar	get
	Pi / Intel Galileo/ARM Cortex/ Arduino).				
Textbooks:					

1. IoT Fundamentals: Networking Technologies, Protocols and Use Cases for Internet of Things, David Hanes, Gonzalo Salgueiro, Patrick Grossetete, Rob Barton and Jerome Henry, Cisco

Press, 2017.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

2. Internet of Things – A hands-on approach, ArshdeepBahga, Vijay Madisetti, Universities Press, 2015

- 1. The Internet of Things Key applications and Protocols, Olivier Hersent, David Boswarthick, Omar Elloumi and Wiley, 2012 (for Unit 2).
- 2. "From Machine-to-Machine to the Internet of Things Introduction to a New Age of Intelligence", Jan Holler, VlasiosTsiatsis, Catherine Mulligan, Stamatis, Karnouskos, Stefan Avesand. David Boyle and Elsevier, 2014.
- 3. Architecting the Internet of Things, Dieter Uckelmann, Mark Harrison, Michahelles and Florian (Eds), Springer, 2011.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	VLSI SIGNAL PROCESSING	L	T	P	C
21D57204c	Program Elective – IV	3	0	0	3
	Semester		I	Ι	
Course Objective	es:				
To stu	dy the existing architectures suitable for VLSI.				
• To und	lerstand the concepts of folding and unfolding algorithms and appl	icati	ons.		
	ign new architectures suitable for VLSI.				
	blement fast convolution algorithms.				
•	s (CO): Student will be able to				
	the existing architectures suitable for VLSI.				
-	stand the concepts of folding and unfolding algorithms and applica	tion	2		
	n new architectures suitable for VLSI.		·		
_	ment fast convolution algorithms.				
UNIT - I	ment tust convolution digorithms.	Ιρ	rture	Hrs:	
	DSP: Typical DSP algorithms, DSP algorithms benefits, Repres				
	ning and Parallel Processing Introduction, Pipelining of FIR Digit				
	ining and Parallel Processing for Low Power Retiming Introduction,				
	olving System of Inequalities, Retiming Techniques	tion	, DC	1111111	OHS
UNIT - II	aving System of Inequalities, Retining Teeninques	Lec	rture	Hrs:	
	folding: Folding- Introduction, Folding Transform, Register				
O	ster minimization in folded architectures, folding of Multirate sys				
	Algorithm for Unfolding, Properties of Unfolding, critical				
	plications of Unfolding.	1 at	ii, O	more	ing
UNIT - III	predictions of emotioning.	Lea	rture	Hrs:	
	ture Design: Introduction, Systolic Array Design Methodolog				
	of Scheduling Vector, Matrix Multiplication and 2D Systoli				
	or Space Representations contain Delays.		ııuj	200	.5,
UNIT - IV	2 Space Representations Committee Design	Leo	cture	Hrs:	
	n: Introduction – Cook - Toom Algorithm – Winogard algo				
	clic Convolution – Design of Fast Convolution algorithm by Inspe			10010	
UNIT - V				Hrs:	
	ign: Digital lattice filter structures, bit level arithmetic, archite				
	rical strength reduction, synchronous, wave and asynchronous pi				
	sumption, Power Analysis, Power Reduction techniques, Po				
Approaches	implient, 10 well imalysis, 10 well iteauction teeminques, 10	<i>3</i>	20		1011
Textbooks:					
	hi, VLSI Digital Signal Processing- System Design and Implement	atio	1. V	Vilev	
Inter Science,			-, '		
	J. While House, T. Kailath ,VLSI and Modern Signal processing , I	Pren	tice I	Hall,	
1985.				,	
Reference Books					
	Yannis Tsividis, Design of Analog – Digital VLSI Circuits for				
	ations and Signal Processing, Prentice Hall, 1994.				
	,VLSI Digital Signal Processing, IEEE Press (NY), 1995				



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	CMOS MIXED SIGNAL IC DESIGN LAB	L	T	P	C	
21D57205		0	0	4	2	
	Semester	II				

Course Objectives:

- To design and simulate op-amp for given specifications
- To design and simulate data converter for given specifications
- To design and simulate PLL and VCO for given specifications
- To understand the Significance of Pre-Layout Simulation and Post-Layout Simulation.

Course Outcomes (CO):

- Design and simulate op-amp for given specifications
- Design and simulate data converter for given specifications
- Design and simulate PLL and VCO for given specifications
- Understand the Significance of Pre-Layout Simulation and Post-Layout Simulation.

List of Experiments:

The students are required to design and implement the Circuit and Layout of the following Experiments using CMOS 130nm Technology.

Cycle 1:

- 1) Fully compensated op-amp with resistor and miller compensation
- 2) High speed comparator design
 - a. Two stage cross coupled clamped comparator
 - b. Strobed Flip-flop
- 3) Data converter

Cycle 2:

- 1) Switched capacitor circuits
 - a. Parasitic sensitive integrator
 - b. Parasitic insensitive integrator
- 2) Design of PLL
- 3) Design of VCO
- 4) Band gap reference circuit
- 5) Layouts of All the circuits Designed and Simulated

Software:

Mentor Graphics/ Cadence/ Tanner/Industry Equivalent Standard Software Tools

Hardware:

Personal Computer with necessary peripherals, configuration and operating System.

References:

- 1. David A johns, Ken Martin, Analog Integrated Circuit Design, Wiley, 2008.
- 2. R. Gregorian and G.C Ternes, Analog MOS Integrated Circuits for Signal Processing, Wiley,1986.
- 3. Roubik Gregorian, Introduction to CMOS OpAmp and Comparators, Wiley, 1999.
- 4. Alan Hastlings, The art of Analog Layout, Wiley, 2005.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	PHYSICAL DESIGN AUTOMATION LAB	L	T	P	C
21D57206		0	0	4	2
	Semester	II			

Course Objectives:

- To learn the implementation of different Physical Design Automation algorithms
- To implement different graph algorithms
- To implement different partitioning algorithms
- To implement different floor planning algorithms
- To implement different routing algorithms

Course Outcomes (CO):

- Learn the implementation of different Physical Design Automation algorithms
- Implement different graph algorithms
- Implement different partitioning algorithms
- Implement different floor planning algorithms
- Implement different routing algorithms

List of Experiments:

Cycle 1:

- 1) Graph algorithms
 - a) Graph search algorithms
 - i. Depth first search
 - ii. Breadth first search
 - b) Spanning tree algorithm
 - i. Kruskal"s algorithm
 - c) Shortest path algorithm
 - i. Dijkstra algorithm
 - ii. Floyd- Warshall algorithm
 - d) Steiner tree algorithm
- 2) Computational geometry algorithm
 - a) Line sweep method
 - b) Extended line sweep method

Cycle 2:

- 3) Partitioning algorithms
 - a) Group migration algorithms
 - I. Kernighan –Lin algorithm
 - II. Extensions of Kernighan-Lin algorithm
 - i) Fiduccias –Mattheyses algorithm
 - ii) Goldberg and Burstein algorithm
 - b) Simulated annealing and evolution algorithms
 - i. Simulated annealing algorithm
 - ii. Simulated evolution algorithm
 - III) Metric allocation method
- 4) Floor planning algorithms
 - i) Constraint based methods
 - ii) Integer programming based methods
 - iii) Rectangular dualization based methods
 - iv) Hierarchical tree based methods



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

- v) Simulated evolution algorithms
- vi) Time driven Floor planning algorithms
- 5) Routing algorithms
 - I) Two terminal algorithms
 - a) Maze routing algorithms
 - i)Lee"s algorithm
 - ii) Soukup"s algorithm
 - iii) Hadlock algorithm
 - b) Line-Probe algorithm
 - c) Shortest path based algorithm
 - II) Multi terminal algorithm
 - a) Stenier tree based algorithm
 - i) SMST algorithm
 - ii) Z-RST algorithm

Software required: C/C++ Programming Language /Relevant software **Text Books:**

- 1) Naveed Shervani, Algorithms for Physical Design Automation, 3rd Edition, Kluwer Academic, 1998.
- 2) Charles J Alpert, Dinesh P Mehta, Sachin S. Sapatnekar, Handbook of Algorithms for Physical Design Automation, CRC Press, 2008.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	BICMOS TECHNOLOGY AND APPLICATIONS	L	T	P	C
21D57301a	Program Elective – V	3	0	0	3
	Semester		II	I	
~ ~ ~ ~ ~					
Course Objective					
	nonstrate in-depth knowledge in BiCMOS Technology.				~ ~
	alyze complex engineering problems critically for conducting res	earch	ın B	1CM	OS
Techn	••	D 1'	г		
	lve engineering problems with wide range of solutions in	Radi	o Fre	eque	ісу
_	ated circuits.				
	lize different digital circuits using BiCMOS Technology s (CO): Student will be able to				
	nstrate in-depth knowledge in BiCMOS Technology.	-amah	in D	:CM	Ω¢
• Analyz Techn	ze complex engineering problems critically for conducting resolvery	zarcii	III D	ICIVI	OS
	ology. engineering problems with wide range of solutions in Radio Fre	naliba	cv In	teoro	ted
circuit		quen	cy III	tegra	icu
	e different digital circuits using BiCMOS Technology				
UNIT - I	e different digital en calls doing Bielites Teelmology	Lec	ture F	Hrs:	
	s Technology: CMOS Process Technology, Bipolar Process Technology				ion
	polar Technologies, BiCMOS Technology, BiCMOS Design Rule		0,5		
UNIT - II			ture I	Hrs:	
	onsiderations: Design Considerations for MOSFET's, Design O				for
_	rs, BiCMOS Device Design Considerations.				
BiCMOS Device	Scaling: MOS Device Scaling, Bipolar Device Scaling.				
UNIT - III		Lec	ture I	Hrs:	
•	g: Modeling of the MOS Transistor: MOSFET Structure and	Opera	ation,	SPI	CE
	OS Transistor, Analytical Model for Short-Channel MOS Devices.				
•	Bipolar Transistor: BJT Structure and Operation, Ebers-Mo	ll Mo	odel,	Bipo	olaı
Models in SPICE				<u> </u>	
UNIT - IV	U-44-1 Ciit D'MOC T-4 D-1- I4 DC Change		ture I		4
_	Integrated Circuits: BiMOS Totem-Pole Inveter: DC Charact Dependence on the Device Parameters, BiCMOS Circuit Design, O				
•	erters Speed, BiCMOS Gates.	comp	armg	CIVI	OS
UNIT - V	etters speed, blewos dates.	Lec	ture F	Irs.	
BiCMOS Digit	al Circuit Applications: Adders, Multiplier, Random	Acces		Iemo	rv
U	ogic Arrays, BiCMOS Logic Cells, BiCMOS Gate Arrays.	1000	,,,	101110	, I J
Textbooks:	<u> </u>				
	nbabi, AbdellatifBellaouar& Mohamed I. Elmasry "Digital Bi	CMC	S In	tegra	ted
	pringer Science+ BusÎness Media, LLC.			_	
2.A L ALVAREZ	Z, BICMOS Technology & Applications, Kluwer Academic Publis	shers.			
Reference Books					
	Samir S. Rofail, Wang-Ling Goh, CMOS/BiCMOS ULSI, Pearso				
•	Denis P. Galipeau, Analog BiCMOS Design: Practices & Pitfalls,				
	ingen, Johan Huijsing, Compact Low-Voltage and High-Speed	CMC	DS, B	iCM	OS
and Bipolar Opera	ational Amplifiers, Springer Science				



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	OPTIMIZATION TECHNIQUES AND APPLICATIONS	L	T	P	C
21D57301b	IN VLSI DESIGN (Program Elective – V)	3	0	0	3
	Semester		II	I	
Course Objecti	ves:				
	rstand basics of statistical modeling				
 To analy 	ze performance of CMOS circuits with respect to power, area and	speed	Į.		
	ire complete knowledge regarding the various algorithms used for	or opt	timiz	ation	of
power a					
Course Outcom	nes (CO): Student will be able to				
 Underst 	and basics of statistical modeling				
 Analyze 	performance of CMOS circuits with respect to power, area and spe	eed			
 Acquire 	complete knowledge regarding the various algorithms used for	r opt	imiz	ation	of
power a	nd area				
UNIT - I		Lect	ure I	Hrs:	
	,	hniqu	,		
	ng-Pelgrom's model, Principle component based modeling,				
O .	rmance modeling- Response surface methodology, delay mode	ling,	inter	conn	ect
delay models.					
UNIT - II			ure I		
	ormance, Power and Yield Analysis: Statistical timing analysis,	-		•	
•	esian networks Leakage models, High level statistical and	-			
statistical analys		aı	nd	pov	ver
	s, High level yield estimation and gate level yield estimation.	т ,		т	
UNIT - III			ure I		1
	ization: Convex sets, convex functions, geometric programmi				
	sis, Generalized geometric programming, geometric programming izing, Floorplanning, wiresizing, Approximation and fitting-N				
	itting, Polynomial fitting.	/101101	illai	11111	ng,
UNIT - IV	itting, i orynomiai ritting.	Locat	ure I	Jrg.	
	ithm: Introduction, GA Technology-Steady State Algorithm				nα
	or VLSI Design, Layout and Test automation- partitioning-auto				
	gy, mappingfor FPGA-Automatic testgeneration-Partitioning algo-				
•	tioning Hybrid genetic-encoding-local improvement-WDFR Con				•
	acement GASP algorithm-unified algorithm.	-p 44116	,011		
UNIT - V		Lect	ure I	Hrs:	
	roceduresand Power Estimation: Global routing-FPGA techn				ng-
	n-test generation in a GA frame work-test generation procedures,				
application of G					
Vs Conventiona					
Textbooks:	•				
	alysis and Optimization for VLSI: Timing and Power -A	shish	Sri	vasta	va
	, David Blaauw, Springer, 2005.				
-	gorithm for VLSI Design, Layout and Test Automation -	-Pinal	kiMa	zumo	ler
E M 1 1. D	nting Hall 1000				

1.Convex Optimization- Stephen Boyd, LievenVandenberghe, Cambridge University Press,2004

E.Mrudnick, Prentice Hall, 1998.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	SoC ARCHITECTURE	L	T	P	C
21D06203a	Program Elective – V	3	0	0	3
	Semester		II	I	
Course Object	ives:				
 To und 	erstand the basics related to SoC architecture and different approach	hes re	elated	l to S	oC
Design					
 To sele 	ct an appropriate robust processor for SoC Design				
 To sele 	ct an appropriate memory for SoC Design.				
 To real 	ize real time case studies				
Course Outcor	nes (CO): Student will be able to				
• Unders	tand the basics related to SoC architecture and different approach	es re	lated	to S	oC
Design					
 Select a 	in appropriated robust processor for SoC Design				
 Select a 	an appropriate memory for SoC Design.				
 Realize 	real time case studies				
UNIT - I		Lect	ure I	Irs:	
Introduction to	the System Approach: System Architecture, Components of the sys	tem, l	Hard	ware	
& Software, P	rocessor Architectures, Memory & Addressing. System level interc	onne	ction	, An	
approach for S	OC Design, System Architecture and Complexity.				
UNIT - II			ure I		
	oduction, Processor Selection for SOC, Basic concepts in Processor				
	s in Processor Microarchitecture, Basic elements in Instruction har				
	peline Delays, Branches, More Robust Processors, Vector Pro	cesso	ors a	nd	
	ction extensions, VLIW Processors, Superscalar Processors				
UNIT - III			ure I	Hrs:	
	for SOC: Overview: SOC external memory, SOC Internal Memory				
	nd Cache memory, Cache Organization, Cache data, Write Policies				
	ent at miss time, Other Types of Cache, Split – I, and D – Caches, I		level		
	Memory System, Models of Simple Processor – memory interaction				
UNIT - IV			ure I	Hrs:	
,	ustomization and Configurability: Interconnect Architectures, Bus: I				
	SOC Standard Buses, Analytic Bus Models, Using the Bus model,	Effe	cts of	Bus	
	d contention time.	_		_	_
SOC Custom					
	Mapping design onto Reconfigurable devices, Instance-				
	Soft Processor, Reconfiguration - overhead analysis and trade	-off	analy	/S1S	on
reconfigurable	Parallelism.	Ŧ.		·	
UNIT - V			ure I		
	dies / Case Studies: SOC Design approach; AES-algorithms, Design	and	evalu	ıatioı	1;
	ssion–JPEG compression.				
Textbooks:					
1. Computer Sy	stem Design System-on-Chip - Michael J. Flynn and Wayne Luk	, W1e	ery In	dia F	'vt

2. ARM System on Chip Architecture - Steve Furber, 2ndEdition, 2000, Addison Wesley

Professional.

Reference Books:



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

- 1. Design of System on a Chip: Devices and Components Ricardo Reis, 1st Ed., 2004, Springer 2.Co-Verification of Hardware and Software for ARM System on Chip Design (EmbeddedTechnology) Jason Andrews Newnes, BK and CDROM.
- 3.System on Chip Verification Methodologies and Techniques –PrakashRashinkar, PeterPaterson and Leena Singh L, 2001, Kluwer Academic Publishers



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

AUDIT COURSE-I



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	ENGLISH FOR RESEARCH PAPER WRITING	L	T	P	C
21DAC101a		2	0	0	0
	Semester			I	
Course Objectiv	es: This course will enable students:				
Understa	nd the essentials of writing skills and their level of readability				
• Learn ab	out what to write in each section				
	ualitative presentation with linguistic accuracy				
Course Outcome	es (CO): Student will be able to				
 Understa 	nd the significance of writing skills and the level of readability				
 Analyze 	and write title, abstract, different sections in research paper				
Develop	the skills needed while writing a research paper				
UNIT - I	9 11	ectur	e Hrs	:10	
10verview of a l	Research Paper- Planning and Preparation- Word Order- Useful 1	Phras	es - E	Break	ing
up Long Sentence	es-Structuring Paragraphs and Sentences-Being Concise and Rem	oving	Red	undaı	ncy
-Avoiding Ambig	guity				
UNIT - II			e Hrs		
	nents of a Research Paper- Abstracts- Building Hypothesis-Re			oblei	n -
Highlight Finding	gs- Hedging and Criticizing, Paraphrasing and Plagiarism, Cauteri	zatio	1		
UNIT - III		ectur	e Hrs	:10	
	ew of the Literature - Methodology - Analysis of the Data-Find	ings	- Dis	cussi	on-
Conclusions-Rec	ommendations.				
UNIT - IV		Le	cture	Hrs:)
	for writing a Title, Abstract, and Introduction			11101	•
UNIT - V		Le	cture	Hrs:)
Appropriate lang	uage to formulate Methodology, incorporate Results, put forth Ar	gume	ents a	nd dr	aw
Conclusions					
Suggested Read	ing				
	R (2006) Writing for Science, Yale University Press (available or	Goo	gle E	Books)
	urriculum of Engineering & Technology PG Courses [Volume-I]				
	006) How to Write and Publish a Scientific Paper, Cambridge Un	versi	ty Pr	ess	
	N (1998), Handbook of Writing for the Mathematical Sciences, S				
Highman					
	Vallwork, English for Writing Research Papers, Springer New Yo	rk Do	ordrec	cht	
Heidelbe	rg London, 2011				



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	DIG A COURT A CANA CONTINUE	L	T	P	С
21DAC101b	DISASTER MANAGEMENT	2	0	0	0
	Semester]	[

Course Objectives: This course will enable students:

- Learn to demonstrate critical understanding of key concepts in disaster risk reduction and humanitarian response.
- Critically evaluatedisasterriskreduction and humanitarian response policy and practice from Multiple perspectives.
- Developanunderstandingofstandardsofhumanitarianresponseandpracticalrelevanceinspecific types of disasters and conflict situations
- Criticallyunderstandthestrengthsandweaknessesofdisastermanagementapproaches, planning and programming in different countries, particularly their home country or the countries they work in

UNIT - I

Introduction:

Disaster:Definition,FactorsandSignificance;DifferenceBetweenHazardandDisaster;Naturaland Manmade Disasters: Difference, Nature, Types and Magnitude.

Disaster Prone Areas in India:

Study of Seismic Zones; Areas Prone to Floods and Droughts, Landslides and Avalanches; Areas Prone to Cyclonic and Coastal Hazards with Special Reference to Tsunami; Post- Disaster Diseases and Epidemics

UNIT - II

Repercussions of Disasters and Hazards:

Economic Damage, Loss of Human and Animal Life, Destruction of Ecosystem. Natural Disasters: Earthquakes, Volcanisms, Cyclones, Tsunamis, Floods, Droughts and Famines, Landslides and Avalanches, Man-made disaster: Nuclear Reactor Meltdown, Industrial Accidents, Oil Slicks and Spills, Outbreaks of Disease and Epidemics, War and Conflicts.

UNIT - III

Disaster Preparedness and Management:

Preparedness: Monitoring of Phenomena Triggering ADisasteror Hazard; Evaluation of Risk: Application of Remote Sensing, Data from Meteorological and Other Agencies, Media Reports: Governmental and Community Preparedness.

UNIT - IV

Risk Assessment Disaster Risk:

Concept and Elements, Disaster Risk Reduction, Global and National Disaster Risk Situation. TechniquesofRiskAssessment,GlobalCo-OperationinRiskAssessmentand Warning, People's Participation in Risk Assessment. Strategies for Survival.

UNIT - V

Disaster Mitigation:

Meaning, Conceptand Strategies of Disaster Mitigation, Emerging Trends In Mitigation. Structural Mitigation and Non-Structural Mitigation, Programs of Disaster Mitigation in India.

Suggested Reading

- 1. R.Nishith, SinghAK, "Disaster Management in India: Perspectives, issues and strategies
- 2. "'New Royal book



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

- Company..Sahni,PardeepEt.Al.(Eds.),"DisasterMitigationExperiencesAndReflections",PrenticeHa ll OfIndia, New Delhi.
- 3. GoelS.L.,DisasterAdministrationAndManagementTextAndCaseStudies",Deep&Deep Publication Pvt. Ltd., New Delhi



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	SANSKR	ITFOR TECHNICAL KNOWLEDGE	L	T	P	C
21DAC101c			2	0	0	0
	I	Semeste	r	1	Ī	ı
Course Objecti	ves: This cours	e will enable students:				
To get a	working know	ledge in illustrious Sanskrit, the scientific la	nguage ii	n the wo	rld	
 Learnin 	g of Sanskrit to	improve brain functioning				
 LearningofSanskrittodevelopthelogicinmathematics,science&othersubjects enhancing the 						
memory	power					
• The eng	ineering schola	rs equipped with Sanskrit will be able to ex	olore the	huge		
 Knowle 	edge from ancie	ntliterature				
Course Outcon	nes (CO): Stud	ent will be able to				
 Underst 	anding basic Sa	nnskrit language				
		ture about science &technology can be under	stood			
 Being a 	logical languag	ge will help to develop logic in students				
UNIT - I						
Alphabets in Sa	anskrit,					
UNIT - II						
Past/Present/Fut	ure Tense, Sim	ple Sentences				
UNIT - III						
Order, Introduct	ion of roots					
UNIT - IV						
Technical infor	rmation about S	anskrit Literature				
UNIT - V						
Technical conc	epts of Enginee	ering-Electrical, Mechanical, Architecture, M	athematic	es		
Suggested Read						
		ishwas, Sanskrit-Bharti Publication, Nev				
2."Teach You	rself Sanskr	it" Prathama Deeksha- VempatiKutu	mbshast	ri, Rash	triyaSa	nskrit
Sansthanam, N						
3."India's Gloa	rious Scientifi	cTradition" Suresh Soni, Ocean books (I) Ltd.,N	ew Del	hi	



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

AUDIT COURSE-II



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code		PEDAGOGY STUDIES	L	T	P	C
21DAC201a		redagog i studies	2	0	0	0
		Semester		1	<u> </u>	
		Semester			-1	
Course Objecti	ves: This cours	se will enable students:				
Reviewe	existingevidence	ceonthereviewtopictoinformprogrammedesigna	ndpolic	y makir	ng	
	•	O, other agencies and researchers.				
 Identify 	critical eviden	ce gaps to guide the development.				
Course Outcom	nes (CO): Stud	ent will be able to				
Students will be	able to unders	tand:				
Whatped countries		icesarebeingusedbyteachersinformalandinform	alclassr	ooms in	develop	ping
		n the effectiveness of these pedagogical practic	oo in u	what		
		hat population of learners?	.es, III v	viiai		
• Howean		on(curricullimandoracticum landtheschoolcurri	culuma	nd ouid:	ance	
material		on(curriculumandpracticum)andtheschoolcurri	culuma	nd guida	ance	
UNIT - I	s best support	effective pedagogy?				k and
UNIT - I Introduction a terminology questions. Over	s best support and Methodole Theories		Concep	tual fra	me wor	
UNIT - I Introduction a terminology	s best support and Methodole Theories	effective pedagogy? ogy: Aims and rationale, Policy back ground, oflearning, Curriculum, Teachereducation. Con	Concep	tual fra	me wor	
UNIT - I Introduction a terminology questions. Over UNIT - II Thematic over	and Methodolo Theories view of metho	effective pedagogy? ogy: Aims and rationale, Policy back ground, oflearning, Curriculum, Teachereducation. Con	Concep	tual fra Iframew	me work	
UNIT - I Introduction a terminology questions. Over UNIT - II Thematic over	and Methodolo Theories view of metho	effective pedagogy? ogy: Aims and rationale, Policy back ground, oflearning, Curriculum, Teachereducation. Condology and Searching.	Concep	tual fra Iframew	me work	earch
UNIT - I Introduction a terminology questions. Over UNIT - II Thematic ove classrooms in c UNIT - III Evidence on the of included stuguidance mater evidence for ef	rview: Pedago leveloping countries. How carrials best support	effective pedagogy? ogy: Aims and rationale, Policy back ground, oflearning, Curriculum, Teachereducation. Condology and Searching.	Conceptual s in for pthstage andthe agth and	rmal are:quality	me work, Res	ormal men t n and ody of
UNIT - I Introduction a terminology questions. Over UNIT - II Thematic ove classrooms in c UNIT - III Evidence on th of included stu guidance mater evidence for ef	rview: Pedago leveloping countries. How carrials best support	effective pedagogy? logy: Aims and rationale, Policy back ground, oflearning, Curriculum, Teachereducation. Condology and Searching. logical practices are being used by teachers intries. Curriculum, Teacher education. logical practices, Methodology for the indemander of teacher education (curriculum and practicum) of teffective pedagogy? Theory of change. Street logical practices. Pedagogic theory and pedagogical practices.	Conceptual s in for pthstage andthe agth and	rmal are:quality	me work, Res	ormal men t n and ody of
UNIT - I Introduction a terminology questions. Over UNIT - II Thematic over classrooms in control UNIT - III Evidence on the of included star guidance mater evidence for eff attitudes and be UNIT - IV Professional de Support from the	rview: Pedago developing countries: How carrials best supporties best supporties and Pedago development: a ne head	effective pedagogy? logy: Aims and rationale, Policy back ground, oflearning, Curriculum, Teachereducation. Condology and Searching. logical practices are being used by teachers intries. Curriculum, Teacher education. logical practices, Methodology for the indemander of teacher education (curriculum and practicum) of teffective pedagogy? Theory of change. Street logical practices. Pedagogic theory and pedagogical practices.	Conceptual sin for pthstage and the agical appropriate appropriate approximately appro	rmal ar e:quality scho cu I nature opproach	me work, Res	men ton and ody of chers'

Researchgapsandfuturedirections: Researchdesign, Contexts, Pedagogy, Teachereducation, Curriculum and assessment, Dissemination and research impact.

Suggested Reading

- 1. AckersJ, HardmanF(2001)ClassroominteractioninKenyanprimaryschools, Compare, 31 (2): 245-261.
- 2. AgrawalM(2004)Curricularreforminschools:Theimportanceofevaluation,Journalof
- 3. Curriculum Studies, 36 (3): 361-379.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

- 4. AkyeampongK(2003) Teacher training in Ghana does it count? Multi-site teachereducation research project (MUSTER) country report 1. London: DFID.
- 5. Akyeampong K, Lussier K, Pryor J, Westbrook J (2013)Improving teaching and learning of basic maths and reading in Africa: Does teacherpreparation count?International Journal Educational Development, 33 (3): 272–282.
- 6. Alexander RJ(2001) Culture and pedagogy: International comparisons in primary education. Oxford and Boston: Blackwell.
 - Chavan M (2003)ReadIndia: A mass scale, rapid, 'learning to read'campaign.
- 7. www.pratham.org/images/resource%20working%20paper%202.pdf.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	CEDEC			L	T	P	C
21DAC201b	SIKES	SSMANAGEMENT BY YOGA		2	0	0	0
		Se	emester		I	I	
Course Objecti	ves: This course v	vill enable students:					
To achie	eve overall health	of body and mind					
To over	come stres						
Course Outcon	nes (CO): Student	will be able to					
Develop	healthy mind in a	a healthy body thus improving soci	al health a	also			
• Improve	efficiency	, , ,					
UNIT - I							
Definitions of I	Eight parts of yog.	(Ashtanga)	•				
UNIT - II							
Yam and Niyar	n.						
UNIT - III							
Do`sand Don't	sin life.						
i) Ahinsa,satya	astheya,bramhach	aryaand aparigrahaii)					
	h,tapa,swadhyay,i	shwarpranidhan					
UNIT - IV							
Asan and Prana	ıyam						
UNIT - V							
i)Variousyogpo	sesand theirbenef	itsformind &body					
		niques and its effects-Types of prana	ayam				
Suggested Read							
		g-Part-I": Janardan SwamiYogabh					
		Internal Nature" by Swami Viv	vekananda	ı, Adv	aita		
Ashrama (Public	cation Department), Kolkata					



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	PERSONALI	TY DEVELOPMENT TH	ROUGHLIFE	L	T	P	C	
21DAC201c		NLIGHTENMENTSKILI		2	0	0	0	
			Semester		I	I		
Course Objecti	ves: This course	will enable students:						
• To learn	to achieve the hi	ghest goal happily						
	_	stable mind, pleasing perso	onality and deteri	nination	l			
	ten wisdom in stu							
	nes (CO): Studen							
		d-Geetawillhelpthestudenting	ndevelopinghisp	ersonalit	yand ac	chieve		
_	est goal in life							
_	The person who has studied Geetawilllead the nation and mankind to peace and prosperity							
	f Neetishatakam v	will help in developing versa	atile personality	of stude	nts			
UNIT - I								
	_	nent of personality						
	20,21,22(wisdom)							
	31,32(pride &hero	oism)						
	28,63,65(virtue)							
UNIT - II								
Neetisatakam-	Holistic developn	nent of personality						
Verses-52,	53,59(dont's)							
Verses-71,	73,75,78(do's)							
UNIT - III								
Approach to da	y to day work and	d duties.						
ShrimadBh	agwadGeeta:Cha	pter2-Verses41,47,48,						
Chapter3-V	Verses 13, 21, 27, 35	,Chapter6-Verses5,13,17,23	3,35,					
Chapter 18-	Verses45,46,48.							
UNIT - IV								
Statements of b	asic knowledge.							
ShrimadBh	agwadGeeta:Cha	pter2-Verses 56,62,68						
Chapter12	-Verses 13, 14, 15,	16,17,18						
Personality	of Rolemodel. S	hrimad Bhagwad Geeta:						
UNIT - V								
Chapter2-V	erses 17,Chapter	3-Verses36,37,42,						
Chapter4-V	/erses18,38,39							
Chapter 18-	- Verses37,38,63							
Suggested Read								
1."SrimadBhaga Kolkata	wadGita"bySwan	niSwarupanandaAdvaitaAsl	nram(Publication	Departr	nent),			
		iti-sringar-vairagya) by P.	Gopinath, Rasht	riyaSan	skrit			



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

OPEN ELECTIVE



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	INDUSTRIAL SAFETY	L	T	P	С
21DOE301b		3	0	0	3
	Semester			III	

Course Objectives:

- To know about Industrial safety programs and toxicology, Industrial laws, regulations and source models
- To understand about fire and explosion, preventive methods, relief and its sizing methods
- To analyse industrial hazards and its risk assessment.

Course Outcomes (CO): Student will be able to

- To list out important legislations related to health, Safety and Environment.
- To list out requirements mentioned in factories act for the prevention of accidents.
- To understand the health and welfare provisions given in factories act.

UNIT - I Lecture Hrs:

Industrial safety: Accident, causes, types, results and control, mechanical and electrical hazards, types, causes and preventive steps/procedure, describe salient points of factories act 1948 for health and safety, wash rooms, drinking water layouts, light, cleanliness, fire, guarding, pressure vessels, etc, Safety color codes. Fire prevention and firefighting, equipment and methods.

UNIT - II Lecture Hrs:

Fundamentals of maintenance engineering: Definition and aim of maintenance engineering, Primary and secondary functions and responsibility of maintenance department, Types of maintenance, Types and applications of tools used for maintenance, Maintenance cost & its relation with replacement economy, Service life of equipment.

UNIT - III Lecture Hrs:

Wear and Corrosion and their prevention: Wear-types, causes, effects, wear reduction methods, lubricants-types and applications, Lubrication methods, general sketch, working andapplications, i. Screw down grease cup, ii. Pressure grease gun, iii. Splash lubrication, iv. Gravity lubrication, v. Wick feed lubrication vi. Side feed lubrication, vii. Ring lubrication, Definition, principle and factors affecting the corrosion. Types of corrosion, corrosion prevention methods.

UNIT - IV Lecture Hrs:

Fault tracing: Fault tracing-concept and importance, decision treeconcept, need and applications, sequence of fault finding activities, show as decision tree, draw decision tree for problems in machine tools, hydraulic, pneumatic,automotive, thermal and electrical equipment's like, I. Any one machine tool, ii. Pump iii. Air compressor, iv. Internal combustion engine, v. Boiler, vi. Electrical motors, Types of faults in machine tools and their general causes.

UNIT - V Lecture Hrs:

Periodic and preventive maintenance: Periodic inspection-concept and need, degreasing, cleaning and repairing schemes, overhauling of mechanical components, overhauling of electrical motor, common troubles and remedies of electric motor, repair complexities and its use, definition, need, steps and advantages of preventive maintenance. Steps/procedure for periodic and preventive maintenance of: I. Machine tools, ii. Pumps, iii. Air compressors, iv. Diesel generating (DG) sets, Program and schedule of preventive maintenance of mechanical and electrical equipment, advantages of preventive maintenance. Repair cycle concept and importance

Textbooks:

- 1. Maintenance Engineering Handbook, Higgins & Morrow, Da Information Services.
- 2. Maintenance Engineering, H. P. Garg, S. Chand and Company.

Reference Books:

- 1. Pump-hydraulic Compressors, Audels, Mcgrew Hill Publication.
- 2. Foundation Engineering Handbook, Winterkorn, Hans, Chapman & Hall London.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

Course Code	BUSINESS ANALYTICS	L	T	P	C
21DOE301c		3	0	0	3
	Semester			III	
Course Objectives:					
	bjective of this course is to give the student a comprehensive undealytics methods.	rstaı	nding	of	
Course Outcomes	(CO): Student will be able to				
Students will demonstrate knowledge of data analytics.					
 Students will demonstrate the ability of think critically in making decisions based on data and deep analytics. 					
	ll demonstrate the ability to use technical skills in predicative and				
	modeling to support business decision-making.				
Students wi	ll demonstrate the ability to translate data into clear, actionable ins				
UNIT - I				Hrs:	
	Overview of Business Analysis, Overview of Requirements, F	Role	of tl	ne Bu	siness
Analyst.		~	~.		
•	oject team, management, and the front line, Handling Stakeholder	Cor	iflicts	S.	
UNIT - II				Hrs:	
	ns Development Life Cycles, Project Life Cycles, Product Life	Cyc]	es, F	Require	ement
Life Cycles.					
UNIT - III		Le	cture	Hrs:	
	ents: Overview of Requirements, Attributes of Good Requ				
	nirement Sources, Gathering Requirements from Stakeholders, Co				
	rming Requirements: Stakeholder Needs Analysis, Decor				
Additive/Subtractiv	e Analysis, Gap Analysis, Notations (UML & BPMN), Flow	/cha	rts, S	Swim	Lane
Flowcharts, Entity-	Relationship Diagrams, State-Transition Diagrams, Data Flow	Diag	rams	, Use	Case
Modeling, Business UNIT - IV	Process Modeling	т.	-4	TT	
	nanta, Procenting Deguinements, Cosislizing Deguinements and			Hrs:	tomas
	nents: Presenting Requirements, Socializing Requirements and of ments. Managing Requirements Assets: Change Control, Requirements Assets: Change Control, Requirements Assets:				tance,
Frioritizing Require	ments. Managing Requirements Assets. Change Control, Require	пеш	8 10	318	
UNIT - V		Le	cture	Hrs:	
Recent Trands in:	Embedded and colleborative business intelligence, Visual of				Data
Storytelling and Da				,	
Textbooks:					
1. Business Analysi	s by James Cadle et al.				
	s by James Cadle et al. nent: The Managerial Process by Erik Larson and, Clifford Gray				
2. Project Managem					
2. Project Management Reference Books:		erjai	ns, D	ara G.	
2. Project Managem Reference Books: 1. Business an	nent: The Managerial Process by Erik Larson and, Clifford Gray	erja	ns, D	ara G.	



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

Course Code	WASTE TO ENERGY	L	T	P	C		
21DOE301e		3	0	0	3		
	Semester	III					
Course Objective	es:						
	and explain energy from waste, classification and devices to	cor	vert	wast	te to		
energy.	1		•				
_	knowledge on biomass pyrolysis, gasification, combustion and co			_			
• To educate on biogas properties ,bio energy system, biomass resources and their classification							
	and biomass energy programme in India. Course Outcomes (CO): Student will be able to						
	about overview of Energy to waste and classification of waste.						
	e knowledge on bio mass pyrolysis, gasification, combustion and	conv	ersic	n pro	ocess		
in detail.							
	knowledge on properties of biogas, biomass resources and programmer of the properties of biogas, biomass resources and programmer of the properties of biogas, biomass resources and programmer of the properties of biogas, biomass resources and programmer of the properties of biogas, biomass resources and programmer of the properties of biogas, biomass resources and programmer of the properties of biogas, biomass resources and programmer of the programmer of the properties of t	ramr	nes t	o cor	ivert		
	nergy in India.	1					
UNIT - I				Hrs:1			
	nergy from Waste: Classification of waste as fuel - Agro base	ed, l	Fores	t resi	idue,		
	MSW – Conversion devices – Incinerators, gasifiers, digestors						
UNIT - II				Hrs:1			
	s: Pyrolysis – Types, slow fast – Manufacture of charcoal –	Met	hods	- Yi	elds		
and application –	Manufacture of pyrolytic oils and gases, yields and applications.						
UNIT - III		Lec	cture	Hrs:	12		
Biomass Gasifica	tion: Gasifiers – Fixed bed system – Downdraft and updraft ga	sifie	rs –	Fluid	ized		
bed gasifiers – De	esign, construction and operation – Gasifier burner arrangement for	or the	ermal	hea	ting		
- Gasifier engin	ne arrangement and electrical power - Equilibrium and kin	netic	cons	sidera	tion		
in gasifier operation	on						
UNIT - IV		Lee	cture	Hrs:	12		
Biomass Combus	tion: Biomass stoves - Improved chullahs, types, some exotic of	lesig	ns, F	ixed	bed		
combustors, Type	es, inclined grate combustors, Fluidized bed combustors, Design	, coi	nstru	ction	and		
operation - Operat	tion of all the above biomass combustors.						
UNIT - V				Hrs:			
Biogas: Propertie	es of biogas (Calorific value and composition) - Biogas plar	nt te	chno	logy	and		
status - Bio ener	gy system - Design and constructional features - Biomass re	esour	ces	and t	their		
classification -							
Biomass convers	ion processes - Thermo chemical conversion - Direct comb	usti	on -	bion	nass		
	lysis and liquefaction - biochemical conversion - anaerobic dig						
	Applications - Alcohol production from biomass - Bio die	esel	prod	luctio	n -		
	energy conversion - Biomass energy programme in India.						
Textbooks:							
1. Non Conv	ventional Energy, Desai, Ashok V., Wiley Eastern Ltd., 2018						
2. Biogas To 2017	echnology - A Practical Hand Book - Khandelwal, K. C. and M	I ahd	i, S.	S., T	МН,		
Reference Books	•						
Telefelle Books							

2. Biomass Conversion and Technology, C. Y. WereKo-Brobby and E. B. Hagan, John Wiley

1. Food, Feed and Fuel from Biomass, Challal, D. S., IBH Publishing Co. Pvt. Ltd., 1991.



M.TECH. IN VLSI/VLSI DESIGN/VLSI YSTEM DESIGN

COMMON COURSE STRUCTURE & SYLLABI

& Sons, 1996

Online Learning Resources:

https://nptel.ac.in/noc/courses/noc19/SEM1/noc19-ch13/https://www.youtube.com/watch?v=x2KmjbCvKTk